

# STR750Fxx STR751Fxx STR752Fxx STR755Fxx

ARM7TDMI-S™ 32-bit MCU with Flash, SMI, 3 std 16-bit timers, PWM timer, fast 10-bit ADC, I2C, UART, SSP, USB and CAN

## **Features**

- Core
  - ARM7TDMI-S 32-bit RISC CPU
  - 54 DMIPS @ 60 MHz

#### Memories

- Up to 256 KB Flash program memory (10k W/E cycles, retention 20 yrs @ 85°C)
- 16 KB Read-While-Write Flash for data (100k W/E cycles, retention 20 yrs@ 85°C)
- Flash Data Readout and Write Protection
- 16KBytes embedded high speed SRAM
- Memory mapped interface (SMI) to ext.
   Serial Flash (64 MB) w. boot capability
- Clock, reset and supply management
  - Single supply 3.3V  $\pm 10\%$  or 5V  $\pm 10\%$
  - Embedded 1.8V Voltage Regulators
  - Int. RC for fast start-up and backup clock
  - Up to 60 MHz operation using internal PLL with 4 or 8 MHz crystal/ceramic osc.
  - Smart Low Power Modes: SLOW, WFI, STOP and STANDBY with backup registers
  - Real-time Clock, driven by low power internal RC or 32.768 kHz dedicated osc, for clock-calendar and Auto Wake-up

## Nested interrupt controller

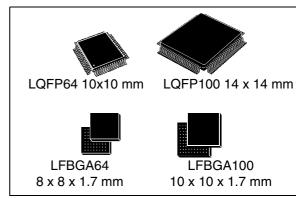
- Fast interrupt handling with 32 vectors
- 16 IRQ priorities, 2 maskable FIQ sources
- 16 external interrupt / wake-up lines

#### DMA

- 4-channel DMA controller
- Circular buffer management
- Support for UART, SSP, Timers, ADC

#### ■ 6 Timers

- 16-bit watchdog timer (WDG)
- 16-bit timer for system timebase functions
- 3 synchronizable timers each with up to 2 input captures and 2 output compare/PWMs.



- 16-bit 6-ch. synchronizable PWM timer
- Dead time generation, edge/center-aligned waveforms and emergency stop
- Ideal for induction/brushless DC motors

#### ■ 8 Communications interfaces

- 1 I<sup>2</sup>C interface
- 3 HiSpeed UARTs w. Modem/LIN capability
- 2 SSP interfaces (SPI or SSI) up to 16 Mb/s
- 1 CAN interface (2.0B Active)
- 1 USB full-speed 12 Mb/s interface with 8 configurable endpoint sizes

#### ■ 10-bit A/D converter

- 16/11 chan. with prog. Scan Mode & FIFO
- Programmable Analog Watchdog feature
- Conversion time: min. 3.75 μs
- Start conversion can be triggered by timers

## ■ Up to 72/38 I/O ports

- 72/38 GPIOs with High Sink capabilities
- Atomic bit SET and RES operations

#### Table 1. Device summary

Reference	Part number
STR750Fxx	STR750FV0, STR750FV1, STR750FV2
STR751Fxx	STR751FR0, STR751FR1, STR751FR2
STR752Fxx	STR752FR0, STR752FR1, STR752FR2
STR755Fxx	STR755FR0, STR755FR1, STR755FR2 STR755FV0, STR755FV1, STR755FV2

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# 1 Description

The STR750 family of 32-bit microcontrollers combines the industry-standard ARM7TDMI® 32-bit RISC core, featuring high performance, very low power, and very dense code, with a comprehensive set of peripherals and ST's latest 0.18µ embedded Flash technology. The STR750 family comprises a range of devices integrating a common set of peripherals as well as USB, CAN and some key innovations like clock failure detection and an advanced motor control timer. It supports both 3.3V and 5V, and it is also available in an extended temperature range (-40 to +105°C). This makes it a genuine general purpose microcontroller family, suitable for a wide range of applications:

- Appliances, brushless motor drives
- USB peripherals, UPS, alarm systems
- Programmable logic controllers, circuit breakers, inverters
- Medical and portable equipment

## 2 Device overview

Table 2. Device overview

Features	STR755FR0 STR755FR1 STR755FR2	STR751FR0/ STR751FR1/ STR751FR2	STR752FR0/ STR752FR1/ STR752FR2	STR755FV0 STR755FV1/ STR755FV2	STR750FV0/ STR750FV1/ STR750FV2							
Flash - Bank 0 (bytes)	64K/128K/256K											
Flash - Bank 1 (bytes)			16K RWV	V								
RAM (bytes)			16K									
Operating Temperature.		•	40 to +85°C / -40 emp40 to + 125	•	*							
Common Peripherals	,	Ps, 1 I2C, 3 timer ake-up lines, 11 /	,	3 timer	Ts, 2 SSPs, 1 I <sup>2</sup> C, s 1 PWM timer, 72 up lines, 16 A/D Channels							
USB/CAN peripherals	None	USB	CAN	None USB+CAN								
Operating Voltage	3.3V or 5V	3.3V	3.3V or	5V								
Packages (x)	T=LQFP64 10x10, H=LFBGA64											



## 3 Introduction

This Datasheet contains the description of the STR750F family features, pinout, Electrical Characteristics, Mechanical Data and Ordering information.

For complete information on the Microcontroller memory, registers and peripherals. Please refer to the STR750F Reference Manual.

For information on the ARM7TDMI-S core please refer to the ARM7TDMI-S Technical Reference Manual available from Arm Ltd.

For information on programming, erasing and protection of the internal Flash memory please refer to the STR7 Flash Programming Reference Manual

For information on third-party development tools, please refer to the http://www.st.com/mcu website.

## 3.1 Functional description

The STR750F family includes devices in 2 package sizes: 64-pin and 100-pin. Both types have the following common features:

#### ARM7TDMI-S™ core with embedded Flash & RAM

STR750F family has an embedded ARM core and is therefore compatible with all ARM tools and software. It combines the high performance ARM7TDMI-S™ CPU with an extensive range of peripheral functions and enhanced I/O capabilities. All devices have on-chip high-speed single voltage FLASH memory and high-speed RAM.

Figure 1 shows the general block diagram of the device family.

## **Embedded Flash memory**

Up to 256 KBytes of embedded Flash is available in Bank 0 for storing programs and data. An additional Bank 1 provides 16 Kbytes of RWW (Read While Write) memory allowing it to be erased/programmed on-the-fly. This partitioning feature is ideal for storing application parameters.

- When configured in burst mode, access to Flash memory is performed at CPU clock speed with 0 wait states for sequential accesses and 1 wait state for random access (maximum 60 MHz).
- When not configured in burst mode, access to Flash memory is performed at CPU clock speed with 0 wait states (maximum 32 MHz)

## **Embedded SRAM**

16 Kbytes of embedded SRAM accessed (read/write) at CPU clock speed with 0 wait states.

## **Enhanced interrupt controller (EIC)**

In addition to the standard ARM interrupt controller, the STR750F embeds a nested interrupt controller able to handle up to 32 vectors and 16 priority levels. This additional hardware block provides flexible interrupt management features with minimal interrupt latency.

## Serial memory interface (SMI)

The Serial Memory interface is directly able to access up to 4 serial FLASH devices. It can be used to access data, execute code directly or boot the application from external memory. The memory is addressed as 4 banks of up to 16 Mbytes each.

## Clocks and start-up

After RESET or when exiting from Low Power Mode, the CPU is clocked immediately by an internal RC oscillator (FREEOSC) at a frequency centered around 5 MHz, so the application code can start executing without delay. In parallel, the 4/8 MHz Oscillator is enabled and its stabilization time is monitored using a dedicated counter.

An oscillator failure detection is implemented: when the clock disappears on the XT1 pin, the circuit automatically switches to the FREEOSC oscillator and an interrupt is generated.

In Run mode, the AHB and APB clock speeds can be set at a large number of different frequencies thanks to the PLL and various prescalers: up to 60 MHz for AHB and up to 32 MHz for APB when fetching from Flash (64 MHz and 32 MHz when fetching from SRAM).

In SLOW mode, the AHB clock can be significantly decreased to reduce power consumption.

The built-in Clock Controller also provides the 48 MHz USB clock directly without any extra oscillators or PLL. For instance, starting from the 4 MHz crystal source, it is possible to obtain in parallel 60 MHz for the AHB clock, 48 MHz for the USB clock and 30 MHz for the APB peripherals.

#### **Boot modes**

At start-up, boot pins are used to select one of five boot options:

- Boot from internal flash
- Boot from external serial Flash memory
- Boot from internal boot loader
- Boot from internal SRAM

Booting from SMI memory allows booting from a serial flash. This way, a specific boot monitor can be implemented. Alternatively, the STR750F can boot from the internal boot loader that implements a boot from UART.

#### **Power supply schemes**

You can connect the device in any of the following ways depending on your application.

- Power Scheme 1: Single external 3.3V power source. In this configuration the
   V<sub>CORE</sub> supply required for the internal logic is generated internally by the main voltage
   regulator and the V<sub>BACKUP</sub> supply is generated internally by the low power voltage
   regulator. This scheme has the advantage of requiring only one 3.3V power source.
- Power Scheme 2: Dual external 3.3V and 1.8V power sources. In this configuration, the internal voltage regulators are switched off by forcing the VREG\_DIS pin to high level. V<sub>CORE</sub> is provided externally through the V<sub>18</sub> and V<sub>18REG</sub> power pins and V<sub>BACKUP</sub> through the V<sub>18\_BKP</sub> pin. This scheme is intended to save power consumption for applications which already provide an 1.8V power supply.
- Power Scheme 3: Single external 5.0V power source. In this configuration the V<sub>CORF</sub> supply required for the internal logic is generated internally by the main voltage

- regulator and the  $V_{BACKUP}$  supply is generated internally by the low power voltage regulator. This scheme has the advantage of requiring only one 5.0V power source.
- Power Scheme 4: Dual external 5.0V and 1.8V power sources. In this configuration, the internal voltage regulators are switched off, by forcing the VREG\_DIS pin to high level. V<sub>CORE</sub> is provided externally through the V<sub>18</sub> and V<sub>18REG</sub> power pins and V<sub>BACKUP</sub> through the V<sub>18</sub> BKP pin. This scheme is intended to provide 5V I/O capability.

**Caution:** When powered by 5.0V, the USB peripheral cannot operate.

#### Low power modes

The STR750F supports 5 low power modes, SLOW, PCG, WFI, STOP and STANDBY.

- SLOW MODE: the system clock speed is reduced. Alternatively, the PLL and the main oscillator can be stopped and the device is driven by a low power clock (f<sub>RTC</sub>). The clock is either an external 32.768 kHz oscillator or the internal low power RC oscillator.
- PCG MODE (Peripheral Clock Gating MODE): When the peripherals are not used, their APB clocks are gated to optimize the power consumption.
- WFI MODE (Wait For Interrupts): only the CPU clock is stopped, all peripherals continue to work and can wake-up the CPU when IRQs occur.
- STOP MODE: all clocks/peripherals are disabled. It is also possible to disable the oscillators and the Main Voltage Regulator (In this case the V<sub>CORE</sub> is entirely powered by V<sub>18\_BKP</sub>). This mode is intended to achieve the lowest power consumption with SRAM and registers contents retained. The system can be woken up by any of the external interrupts / wake-up lines or by the RTC timer which can optionally be kept running. The RTC can be clocked either by the 32.768 kHz Crystal or the Low Power RC Oscillator.
  - Alternatively, STOP mode gives flexibility to keep the either main oscillator, or the Flash or the Main Voltage Regulator enabled when a fast start after wake-up is preferred (at the cost of some extra power consumption).
- STANDBY MODE: This mode (only available in single supply power schemes) is intended to achieve the lowest power consumption even when the temperature is increasing. The digital power supply (V<sub>CORE</sub>) is completely removed (no leakage even at high ambient temperature). SRAM and all register contents are lost. Only the RTC remains powered by V<sub>18\_BKP</sub> The STR750F can be switched back from STANDBY to RUN mode by a trigger event on the WKP\_STDBY pin or an alarm timeout on the RTC counter.

#### Caution:

It is important to bear in mind that it is forbidden to remove power from the V<sub>DD\_IO</sub> power supply in any of the Low Power Modes (even in STANDBY MODE).

#### **DMA**

The flexible 4-channel general-purpose DMA is able to manage memory to memory, peripheral to memory and memory to peripheral transfers. The DMA controller supports circular buffer management avoiding the generation of interrupts when the controller reaches the end of the buffer.

The DMA can be used with the main peripherals: UART0, SSP0, Motor control PWM timer (PWM), standard timer TIM0 and ADC.

#### RTC (real-time clock)

The real-time clock provides a set of continuously running counters which can be used with suitable software to provide a clock calendar function, and provides an alarm interrupt and a

periodic interrupt. It is clocked by an external 32.768 kHz oscillator or the internal low power RC oscillator. The RC has a typical frequency of 300 kHz and can be calibrated.

## WDG (watchdog timer)

The watchdog timer is based on a 16-bit downcounter and 8-bit prescaler. It can be used as watchdog to reset the device when a problem occurs, or as free running timer for application time out management.

## Timebase timer (TB)

The timebase timer is based on a 16-bit auto-reload counter and not connected to the I/O pins. It can be used for software triggering, or to implement the scheduler of a real-time operating system.

## Synchronizable standard timers (TIM2:0)

The three standard timers are based on a 16-bit auto-reload counter and feature up to 2 input captures and 2 output compares (for external triggering or time base / time out management). They can work together with the PWM timer via the Timer Link feature for synchronization or event chaining. In reset state, timer Alternate Function I/Os are connected to the same

I/O ports in both 64-pin and 100-pin devices. To optimize timer functions in 64-pin devices, timer Alternate Function I/Os can be connected, or "remapped", to other I/O ports as summarized in *Table 3* and detailed in *Table 6*. This remapping is done by the application via a control register.

Table 3. Standard timer alternate function I/Os

		Nui	mber of alternate fun	ction I/Os
Star	ndard timer functions	100-pin	64-pin p	oackage
		package	Default mapping	Remapped
TIM 0	Input Capture	2	1	2
I IIVI O	Output Compare/PWM	2	1	2
TIM 1	Input Capture	2	1	1
I IIVI I	Output Compare/PWM	2	1	1
TIM 2	Input Capture	2	2	2
1 11VI Z	Output Compare/PWM	2	1	2

Any of the standard timers can be used to generate PWM outputs. One timer (TIM0) is mapped to a DMA channel.

## Motor control PWM timer (PWM)

The Motor Control PWM Timer (PWM) can be seen as a three-phase PWM multiplexed on 6 channels. The 16-bit PWM generator has full modulation capability (0...100%), edge or centre-aligned patterns and supports dead-time insertion. It has many features in common with the standard TIM timers which has the same architecture and it can work together with the TIM timers via the Timer Link feature for synchronization or event chaining. The PWM timer is mapped to a DMA channel.

#### I2C bus

The I<sup>2</sup>C bus interface can operate in multi-master and slave mode. It can support standard and fast modes (up to 400KHz).

## High speed universal asynch. receiver transmitter (UART)

The three UART interfaces are able to communicate at speeds of up to 2 Mbit/s. They provide hardware management of the CTS and RTS signals and have LIN Master capability.

To optimize the data transfer between the processor and the peripheral, two FIFOs (receive/transmit) of 16 bytes each have been implemented.

One UART can be served by the DMA controller (UART0).

## Synchronous serial peripheral (SSP)

The two SSPs are able to communicate up to 8 Mbit/s (SSP1) or up to 16 Mbit/s (SSP0) in standard full duplex 4-pin interface mode as a master device or up to 2.66 Mbit/s as a slave device. To optimize the data transfer between the processor and the peripheral, two FIFOs (receive/transmit) of 8 x 16 bit words have been implemented. The SSPs support the Motorola SPI or TI SSI protocols.

One SSP can be served by the DMA controller (SSP0).

## Controller area network (CAN)

The CAN is compliant with the specification 2.0 part B (active) with a bit rate up to 1Mbit/s. It can receive and transmit standard frames with 11-bit identifiers as well as extended frames with 29-bit identifiers. Up to 32 message objects are handled through an internal RAM buffer. In LQFP64 devices, CAN and USB cannot be connected simultaneously.

#### Universal serial bus (USB)

The STR750F embeds a USB device peripheral compatible with the USB Full speed 12Mbs. The USB interface implements a full speed (12 Mbit/s) function interface. It has software configurable endpoint setting and suspend/resume support. The dedicated 48 MHz clock source is generated from the internal main PLL.  $V_{DD}$  must be in the range 3.3V±10% for USB operation.

## ADC (analog to digital converter)

The 10-bit Analog to Digital Converter, converts up to 16 external channels (11 channels in 64-pin devices) in single-shot or scan modes. In scan mode, continuous conversion is performed on a selected group of analog inputs. The minimum conversion time is  $3.75 \,\mu s$  (including the sampling time).

The ADC can be served by the DMA controller.

An analog watchdog feature allows you to very precisely monitor the converted voltage of up to four channels. An IRQ is generated when the converted voltage is outside the programmed thresholds.

The events generated by TIM0, TIM2 and PWM timers can be internally connected to the ADC start trigger, injection trigger, and DMA trigger respectively, to allow the application to synchronize A/D conversion and timers.

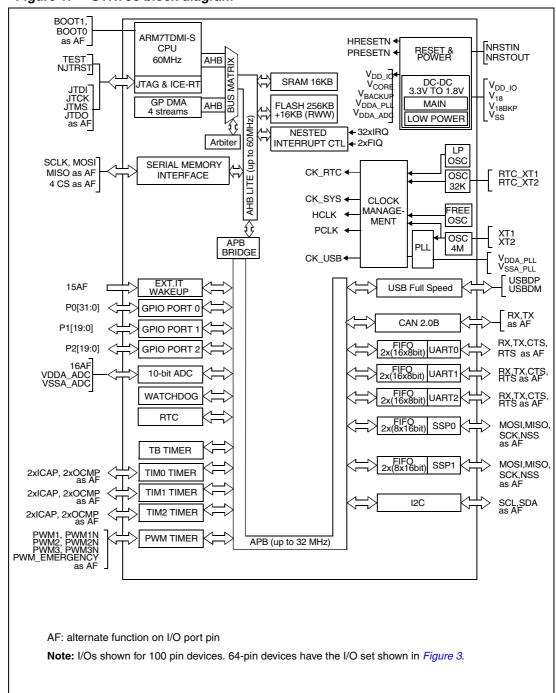
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## **GPIOs** (general purpose input/output)

Each of the 72 GPIO pins (38 GPIOs in 64-pin devices) can be configured by software as output (push-pull or open-drain), as input (with or without pull-up or pull-down) or as Peripheral Alternate Function. Port 1.15 is an exception, it can be used as general-purpose input only or wake-up from STANDBY mode (WKP\_STDBY). Most of the GPIO pins are shared with digital or analog alternate functions.

# 3.2 Block diagram

Figure 1. STR750 block diagram



#### Pin description 4

Figure 2. LQFP100 pinout

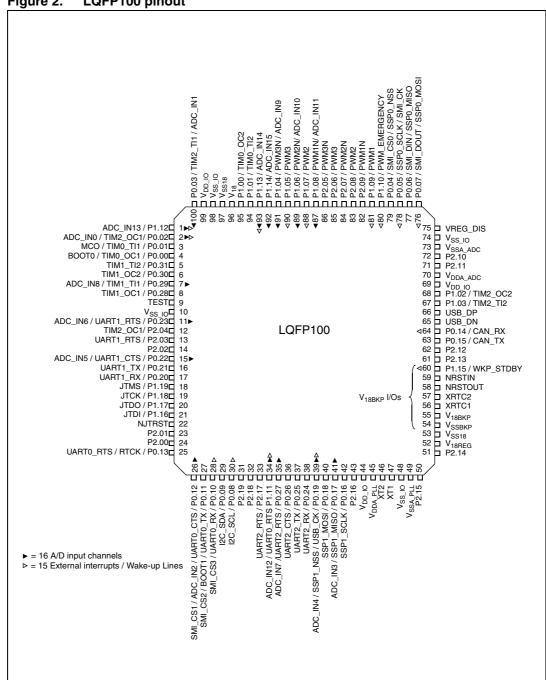


Figure 3. LQFP64 pinout

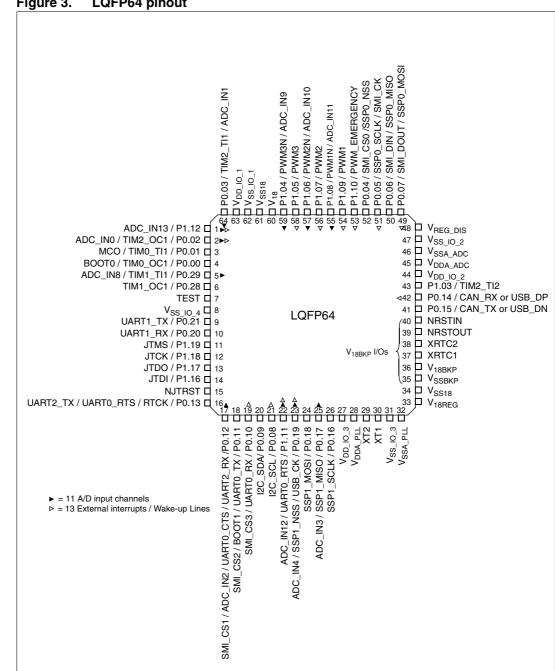


Table 4. LFBGA100 ball connections

	1	2	3	4	5	6	7	8	9	10
A	P0.03	P1.13	P1.14	P1.04	P1.06	P1.08	P0.05	P0.06	P0.07	P1.02
В	P1.12	P0.02	P0.01	P1.05	P1.07	P1.09	P0.04	P2.13	P1.03	P2.10
С	P0.31	P0.00	V <sub>DD_IO</sub>	V <sub>18</sub>	P1.10	P2.09	V <sub>SS_IO</sub>	V <sub>SSA_ADC</sub>	P2.11	USB_DP
D	P0.29	P0.30	V <sub>SS_IO</sub>	V <sub>SS18</sub>	P1.01	P1.15	V <sub>DD_IO</sub>	V <sub>DDA_ADC</sub>	P2.12	USB_DN
E	P0.28	P0.23	P0.22	V <sub>SS_IO</sub>	TEST	P1.00	NRSTOUT	VREG_DIS	NRSTIN	P0.14
F	P2.03	P0.21	P0.20	P2.02	P2.04	P2.05	P2.06	V <sub>SS18</sub>	V <sub>SSBKP</sub>	P0.15
G	NJTRST	P1.18	P1.19	P2.01	P2.00	P2.07	2.08	V <sub>18REG</sub>	V <sub>18BKP</sub>	XRTC2
Н	P0.13	P1.16	P1.17	P2.19	P2.18	P2.17	P0.24	P2.14	P2.16	XRTC1
J	P0.11	P0.12	P1.11	P0.27	P0.19	P0.26	P0.25	P2.15	V <sub>DD_IO</sub>	V <sub>SS_IO</sub>
K	P0.10	P0.09	P0.08	P0.18	P0.17	P0.16	XT1	XT2	V <sub>DDA_PLL</sub>	V <sub>SSA_PLL</sub>

Table 5. LFBGA64 ball connections

	1	2	3	4	5	6	7	8
Α	P0.03	V <sub>SS_IO</sub>	P1.04	P1.06	P1.08	P0.05	P0.06	P0.07
В	P1.12	$V_{DD\_IO}$	P1.05	P1.07	P1.09	P0.04	P1.10	P1.03
С	P0.01	P0.02	P0.00	V <sub>18</sub>	V <sub>SS18</sub>	$V_{DD\_IO}$	V <sub>SS_IO</sub>	P0.14
D	P0.29	P0.28	TEST	V <sub>SS_IO</sub>	VREG_DIS	V <sub>DDA_ADC</sub>	V <sub>SSA_ADC</sub>	P0.15
E	P1.18	P1.19	P0.20	P0.21	NRSTOUT	NRSTIN	V <sub>18BKP</sub>	XRTC2
F	P0.13	NJTRST	P1.16	P1.17	V <sub>18REG</sub>	V <sub>SS18</sub>	V <sub>SSBKP</sub>	XRTC1
G	P0.11	P0.12	P1.11	P0.19	V <sub>DD_IO</sub>	V <sub>SS_IO</sub>	V <sub>DDA_PLL</sub>	V <sub>SSA_PLL</sub>
н	P0.10	P0.09	P0.08	P0.17	P0.18	P0.16	XT2	XT1

# 4.1 Pin description table

Legend / abbreviations for *Table 6*:

**Type:** I = input, O = output, S = supply,

Input levels: All Inputs are LVTTL at  $V_{DD\ IO} = 3.3V + /-0.3V$  or TTL

at  $V_{DD\ IO} = 5V \pm 0.5V$ . In both cases,  $T_T$  means

 $V_{ILmax} = 0.8V V_{IHmin} = 2.0V$ 

**Inputs:** All inputs can be configured as floating or with

internal weak pull-up or pull down (pu/pd)

Outputs: All Outputs can be configured as Open Drain (OD) or

Push-Pull (PP) (see also note 6 below *Table 6*). There are 3 different types of Output with different

drives and speed characteristics:

- O8: f<sub>max</sub> = 40 MHz on C<sub>L</sub>=50pF and 8 mA static drive capability for V<sub>OL</sub>=0.4V and up to 20 mA for V<sub>OL</sub>=1.3V (see *Output driving current on page 55*)

 O4: f<sub>max</sub> = 20 MHz on C<sub>L</sub>=50pF and 4 mA static drive capability for V<sub>OL</sub>=0.4V (see Output driving

current on page 55)

 O2: f<sub>max</sub> = 10 MHz on C<sub>L</sub>=50pF and 2 mA static drive capability of for V<sub>OL</sub>=0.4V (see Output driving

current on page 55)

External interrupts/wake-up lines: EITx

#### Port reset state

The reset state of the I/O ports is GPIO input floating. Exceptions are P1[19:16] and P0.13 which are configured as JTAG alternate functions:

- The JTAG inputs (JTDI, JTMS and JTDI) are configured as input floating and are ready to accept JTAG sequences.
- The JTAG output JTDO is configured as floating when idle (no JTAG operation) and is configured in output push-pull only when serial JTAG data must be output.
- The JTAG output RTCK is always configured as output push-pull. It outputs '0' level during the reset phase and then outputs the JTCK input signal resynchronized 3 times by the internal AHB clock.
- The GPIO\_PCx registers do not control JTAG AF selection, so the reset values of GPIO\_PCx for P1[19:16] and P0. 13 are the same as other ports. Refer to the GPIO section of the STR750 Reference Manual for the register description and reset values.
- P0.11 and P0.00 are sampled by the boot logic after reset, prior to fetching the first word of user code at address 0000 0000h.
- When booting from SMI (and only in this case), the reset state of the following GPIOs is "SMI alternate function output enabled":
  - P0.07 (SMI\_DOUT)
  - P0.05 (SMI\_CLK)
  - P0.04 (SMI\_CS0)
  - P0.06 (SMI DIN)

Note that the other SMI pins: SMI\_CS1,2,3 (P0.12, P0.11, P0.10) are not affected.

To avoid excess power consumption, unused I/O ports must be tied to ground.

Table 6. STR750F pin description

	Pin	n°					In	put		O	utpu	ıt	5			
LQFP100 <sup>(1)</sup>	LFBGA100 <sup>(1)</sup>	LQFP64 <sup>(2)</sup>	LFBGA64 <sup>(2)</sup>	Pin name	Туре	Input Level	floating	pd/nd	Ext. int /Wake-up	Capability	OD (3)	PP	Usable in Standby	Main function (after reset)	Alternate	e function
1	B1	1	B1	P1.12 / ADC_IN13	I/O	T <sub>T</sub>	х	Х	EIT12	O8	Х	Х		Port 1.12	ADC: Analog input 13	
2	B2	2	C2	P0.02 / TIM2_OC1 / ADC_IN0	I/O	T <sub>T</sub>	x	х	EIT0	O8	х	х		Port 0.02	TIM2: Output Compare 1 <sup>(4)</sup>	ADC: Analog input 0
3	ВЗ	3	C1	P0.01 / TIM0_TI1 / MCO	I/O	T <sub>T</sub>	х	х		O8	х	х		Port 0.01	TIM0: Input Capture / trigger / external clock 1	Main Clock Output
4	C2	4	СЗ	P0.00 / TIM0_OC1 / BOOT0	I/O	T <sub>T</sub>	x	Х		О8	x	x		Port 0.00 / Boot mode selection input 0	TIM0: Output Con	npare 1
5	C1			P0.31 / TIM1_TI2	I/O	T <sub>T</sub>	х	Х		O2	х	Х		Port 0.31	TIM1: Input Captu external clock 2	ure / trigger /
6	D2			P0.30 / TIM1_OC2	I/O	T <sub>T</sub>	х	Х		O2	х	Х		Port 0.30	TIM1: Output Con	npare 2

Table 6. STR750F pin description (continued)

	Pin	n°		K/SUF pin de				put		ĺ	utpu	ıt					
	FIII							put			utpu		gp				
LQFP100 <sup>(1)</sup>	LFBGA100 <sup>(1)</sup>	LQFP64 <sup>(2)</sup>	LFBGA64 <sup>(2)</sup>	Pin name	Туре	Input Level	floating	pd/nd	Ext. int /Wake-up	Capability	OD (3)	PP	Usable in Standby	Main function (after reset)	Alternate	e function	
7	D1	5	D1	P0.29 / TIM1_TI1 / ADC_IN8	I/O	T <sub>T</sub>	х	Х		02	Х	Х		Port 0.29	TIM1: Input Capture 1	ADC: Analog input 8	
8	E1	6	D2	P0.28 / TIM1_OC1	I/O	T <sub>T</sub>	x	Х		02	Х	Х		Port 0.28	TIM1: Output Cor	npare 1	
9	E5	7	D3	TEST	I									Reserved, mu	ıst be tied to groun	d	
10	E4	8	D4	VSS_IO	S									Ground Voltag	ge for digital I/Os		
11	E2			P0.23 / UART1_RTS / ADC_IN6	I/O	T <sub>T</sub>	x	Х		O2	х	Х		Port 0.23	UART1: Ready To Send output <sup>(4)</sup>	ADC analog input	
12	F5			P2.04 / TIM2_OC1	I/O	T <sub>T</sub>	х	х		O2	х	Х		Port 2.04	TIM2: Output Compare 1 <sup>(4)</sup>		
13	F1			P2.03 / UART1_RTS	I/O	T <sub>T</sub>	x	Х		O2	Х	X		Port 2.03	UART1: Ready To Send output <sup>(4)</sup>		
14	F4			P2.02	I/O	$T_T$	X	Х		O2	Х	Χ		Port 2.02			
15	E3			P0.22 / UART1_CTS / ADC_IN5	I/O	T <sub>T</sub>	x	Х		O2	х	Х		Port 0.22	UART1: Clear To Send input	ADC: Analog input 5	
16	F2	9	E4	P0.21 / UART1_TX	I/O	T <sub>T</sub>	х	Х		02	Х	Х		Port 0.21	UART1: Transmit (remappable to P		
17	F3	10	E3	P0.20 / UART1_RX	I/O	T <sub>T</sub>	х	Х		O2	х	Х		Port 0.20	UART1: Receive (remappable to P		
18	G3	11	E2	P1.19 / JTMS	I/O	T <sub>T</sub>	Х	Х		02	Х	X		JTAG mode selection input <sup>(6)</sup>	Port 1.19		
19	G2	12	E1	P1.18 / JTCK	I/O	T <sub>T</sub>	Х	Х		02	Х	Х		JTAG clock input <sup>(6)</sup>	Port 1.18		
20	НЗ	13	F4	P1.17 / JTDO	I/O	T <sub>T</sub>	Х	Х		08	Х	Х		JTAG data output <sup>(6)</sup>	Port 1.17		
21	H2	14	F3	P1.16 / JTDI	I/O	T <sub>T</sub>	х	х		02	Х	Х		JTAG data input <sup>(6)</sup>	Port 1.16		
22	G1	15	F2	NJTRST	-1	T <sub>T</sub>								JTAG reset in	put <sup>(5)</sup>		
23	G4			P2.01	I/O	T <sub>T</sub>	X	Х		O2	Х	Χ		Port 2.01			
24	G5			P2.00	I/O	$T_T$	X	Х		O2	Х	Χ		Port 2.00			
															Port 0.13		
25	H1	16	F1	P0.13 / RTCK / UART0_RTS UART2_TX	I/O	T <sub>T</sub>	Х	Х		O8	х	Х		JTAG return clock output <sup>(6)</sup>	UART0: Ready To Send output <sup>(4)</sup>	UART2: Transmit Data output (when remapped) <sup>(8)</sup>	

Table 6. STR750F pin description (continued)

	Pin	n°					In	put		C	utpu	ıt	>			
LQFP100 <sup>(1)</sup>	LFBGA100 <sup>(1)</sup>	LQFP64 <sup>(2)</sup>	LFBGA64 <sup>(2)</sup>	Pin name	Туре	Input Level	floating	pd/nd	Ext. int /Wake-up	Capability	OD (3)	PP	Usable in Standby	Main function (after reset)	Alternate	e function
26	J2	17	G2	P0.12 / UART2_RX / UART0_CTS / ADC_IN2 / SMI_CS1	I/O	T <sub>T</sub>	x	x		O4	x	х		Port 0.12	UART0: Clear To Send input Serial Memory Interface: chip select output 1	ADC: Analog input 2 UART2: Receive Data input (when remapped) <sup>(8)</sup>
27	J1	18	G1	P0.11 / UARTO_TX / BOOT1 / SMI_CS2	I/O	T <sub>T</sub>	x	х		O4	х	х		Port 0.11/Boot mode selection input 1	UART0: Transmit data output	Serial Memory Interface: chip select output 2
28	K1	19	H1	P0.10 / UARTO_RX / SMI_CS3	I/O	T <sub>T</sub>	х	х	EIT4	O2	х	х		Port 0.10	UART0: Receive Data input	Serial Memory Interface: chip select output 3
29	K2	20	H2	P0.09 / I2C_SDA	I/O	T <sub>T</sub>	х	Х		04	Х	Х		Port 0.09	I2C: Serial Data	
30	K3	21	НЗ	P0.08 / I2C_SCL	I/O	T <sub>T</sub>	х	Х	EIT3	04	Х	Х		Port 0.08	I2C: Serial clock	
31	H4			P2.19	I/O	T <sub>T</sub>	х	Х		02	Х	Х		Port 2.19		
32	H5			P2.18	I/O	T <sub>T</sub>	Х	Х		O2	Х	Х		Port 2.18		
33	H6			P2.17 / UART2_RTS	I/O	T <sub>T</sub>	х	Х		O2	Х	Х		Port 2.17	UART2: Ready To	Send output <sup>(4)</sup>
34	J3	22	G3	P1.11 /UARTO_RTS ADC_IN12	I/O	T <sub>T</sub>	x	х	EIT11	O8	х	х		Port 1.11	UART0: Ready To Send output <sup>(4)</sup>	ADC: Analog input 12
35	J4			P0.27 / UART2_RTS / ADC_IN7	I/O	T <sub>T</sub>	x	X		O2	Х	Х		Port 0.27	UART2: Ready To Send output <sup>(8)</sup>	ADC: Analog input 7
36	J6			P0.26 / UART2_CTS	I/O	T <sub>T</sub>	х	Х		O2	Х	Х		Port 0.26	UART2: Clear To	Send input
37	J7			P0.25 / UART2_TX	I/O	T <sub>T</sub>	х	Х		02	Х	Х		Port 0.25	UART2: Transmit (remappable to Po	
38	H7			P0.24 / UART2_RX	I/O	T <sub>T</sub>	x	Х		02	Х	Х		Port 0.24	UART2: Receive (remappable to Po	data input 0.12) <sup>(8)</sup>
39	J5	23	G4	P0.19/USB_CK/ SSP1_NSS/	I/O	T <sub>T</sub>	x	X	EIT6	O2	x	х		Port 0.19	SSP1: Slave select input (remappable to P0.11) <sup>(8)</sup>	ADC: Analog input 4
				ADC_IN4											USB: 48 MHz Clock input	
40	K4	24	H5	P0.18 / SSP1_MOSI	I/O	T <sub>T</sub>	х	Х		02	Х	Х		Port 0.18	SSP1: Master out (remappable to Po	/slave in data 0.10) <sup>(8)</sup>
41	K5	25	H4	P0.17 / SSP1_MISO / ADC_IN3	I/O	T <sub>T</sub>	X	Х		O2	x	х	_	Port 0.17	SSP1: Master in/slave out data (remappable to P0.09) <sup>(8)</sup>	ADC: Analog input 3
42	K6	26	H6	P0.16 / SSP1_SCLK	I/O	T <sub>T</sub>	х	Х		O2	х	х		Port 0.16	SSP1: serial clock P0.08) <sup>(8)</sup>	(remappable to

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Table 6. STR750F pin description (continued)

	Pin	n°		H7301 pili de				put			utpu	ıt	>			
LQFP100 <sup>(1)</sup>	LFBGA100 <sup>(1)</sup>	LQFP64 <sup>(2)</sup>	LFBGA64 <sup>(2)</sup>	Pin name	Туре	Input Level	floating	pd/nd	Ext. int /Wake-up	Capability	OD (3)	PP	Usable in Standby	Main function (after reset)	Alternate function	
43	Н9			P2.16	I/O	T <sub>T</sub>	Х	Χ		02	Х	Х		Port 2.16		
44	J9	27	G5	VDD_IO	S									Supply voltag	e for digital I/Os	
45	K9	28	G7	VDDA_PLL	S									Supply voltag	e for PLL	
46	K8	29	H7	XT2										4 MHz main o	oscillator	
47	K7	30	Н8	XT1												
48	J10	31	G6	VSS_IO	S									Ground voltage	ge for digital I/Os	
49	K10	32	G8	VSSA_PLL	S									Ground voltage	ge for PLL	
50	J8			P2.15	I/O	T <sub>T</sub>	X	Х		02	Х	Х		Port 2.15		
51	H8			P2.14	I/O	T <sub>T</sub>	X	Х		02	Х	Х		Port 2.14		
52	G8	33	F5	V18REG	S									external capa V18REG and To be connec	for main voltage regulator. Requires scitors of at least 10µF between VSS18. See <i>Figure 4.2</i> . ted to the 1.8V external power supply ded regulators are not used,	
53	F8	34	F6	VSS18	S									Ground Volta	ge for the main voltage regulator	
54	F9	35	F7	VSSBKP	S									Stabilization f	or low power voltage regulator.	
55	G9	36	E7	V18BKP	S									Requires extended between V18 To be connected to the conn	ge for the low power voltage regulator. ernal capacitors of at least 1µF BKP and VSSBKP. See <i>Figure 4.2</i> . ted to the 1.8V external power supply ded regulators are not used,	
56	H10	37	F8	XRTC1									Х	00 141	stantan Daalkinsa Olaala	
57	G10	38	E8	XRTC2									Х	32 KHZ OSCIIIA	ator for Realtime Clock	
58	E7	39	E5	NRSTOUT	0								Х	Reset output		
59	E9	40	E6	NRSTIN	I	T <sub>T</sub>							Х	Reset input		
60	D6			P1.15 / WKP_STDBY	I	T <sub>T</sub>	х		EIT15				Х	Port 1.15	Wake-up from STANDBY input pin	
61	B8			P2.13	I/O	T <sub>T</sub>	X	Х		02	Х	Х		Port 2.13		
62	D9			P2.12	I/O	T <sub>T</sub>	X	X		O2	Х	Х		Port 2.12		
63	F10	41 (7)	D8 (7)	P0.15 / CAN_TX	I/O	T <sub>T</sub>	x	X		O2	х	х		Port 0.15	CAN: Transmit data output	
64	E10	42 (7)	C8 (7)	P0.14 / CAN_RX	I/O	T <sub>T</sub>	x	Х	EIT5	O2	Х	Х		Port 0.14	CAN: Receive data input	
65	D10	41 (7)	D8 (7)	USB_DN	I/O									USB: bidirect	ional data (data -)	
66	C10	42 (7)	C8 (7)	USB_DP	I/O									USB: bidirect	ional data (data +)	
67	В9	43	B8	P1.03 / TIM2_TI2	I/O	T <sub>T</sub>	x	X		O2	х	х		Port 1.03	TIM2: Input Capture / trigger / external clock 2 (remappable to P0.07) <sup>(8)</sup>	

Table 6. STR750F pin description (continued)

	Pin	n°		H7301 pill de				put			utpu	ıt	>			
LQFP100 <sup>(1)</sup>	LFBGA100 <sup>(1)</sup>	LQFP64 <sup>(2)</sup>	LFBGA64 <sup>(2)</sup>	Pin name	Туре	Input Level	floating	pd/nd	Ext. int /Wake-up	Capability	OD (3)	PP	Usable in Standby	Main function (after reset)	Alternate	e function
68	A10			P1.02 / TIM2_OC2	I/O	T <sub>T</sub>	х	х		02	Х	Х		Port 1.02	TIM2: Output com (remappable to P	npare 2 0.06) <sup>(8)</sup>
69	D7	44	C6	VDD_IO	S									Supply Voltag	e for digital I/Os	
70	D8	45	D6	VDDA_ADC	S									Supply Voltag	e for A/D converte	r
71	C9			P2.11	I/O	T <sub>T</sub>	Х	Х		02	Х	Х		Port 2.11		
72	B10			P2.10	I/O	T <sub>T</sub>	Х	Х		02	Х	Х		Port 2.10		
73	C8	46	D7	VSSA_ADC	S									Ground Voltage	ge for A/D converte	er
74	C7	47	C7	VSS_IO	S									Ground Voltage	ge for digital I/Os	
75	E8	48	D5	VREG_DIS	I	T <sub>T</sub>								Voltage Regu	lator Disable input	
76	A9	49	A8	P0.07 / SMI_DOUT / SSP0_MOSI	I/O	T <sub>T</sub>	х	Х	EIT2	04	х	х		Port 0.07	Serial Memory Interface: data output	SSP0: Master out Slave in data
77	A8	50	A7	P0.06 / SMI_DIN / SSP0_MISO	I/O	T <sub>T</sub>	X	Х		04	х	х		Port 0.06	Serial Memory Interface: data input	SSP0: Master in Slave out data
78	A7	51	A6	P0.05 / SSP0_SCLK / SMI_CK	I/O	T <sub>T</sub>	x	Х	EIT1	O4	х	х		Port 0.05	SSP0: Serial clock	Serial Memory Interface: Serial clock output
79	B7	52	В6	P0.04 / SMI_CS0 / SSP0_NSS	I/O	T <sub>T</sub>	x	X		04	Х	х		Port 0.04	Serial Memory Interface: chip select output 0	SSP0: Slave select input
80	C5	53	В7	P1.10 PWM_EMERGE NCY	I/O	T <sub>T</sub>	x	Х	EIT10	O2	х	х		Port 1.10	PWM: Emergency	/ input
81	В6	54	В5	P1.09 / PWM1	I/O	T <sub>T</sub>	Х	Х	EIT9	04	Х	Х		Port 1.09	PWM: PWM1 out	put
82	C6			P2.09 / PWM1N	I/O	T <sub>T</sub>	х	Х		02	х	х		Port 2.09	PWM: PWM1 con output <sup>(4)</sup>	nplementary
83	G7			P2.08 / PWM2	I/O	T <sub>T</sub>	X	Х		O2	Х	Х		Port 2.08	PWM: PWM2 out	put <sup>(4)</sup>
84	G6			P2.07 / PWM2N	I/O	T <sub>T</sub>	х	Х		O2	х	Х		Port 2.07	PWM: PWM2 con output <sup>(4)</sup>	nplementary
85	F7			P2.06 / PWM3	I/O	T <sub>T</sub>	X	Х		O2	Х	Х		Port 2.06	PWM: PWM3 out	put <sup>(4)</sup>
86	F6			P2.05 / PWM3N	I/O	T <sub>T</sub>	х	Х		O2	х	Х		Port 2.05	PWM: PWM3 con output <sup>(4)</sup>	nplementary
87	A6	55	<b>A</b> 5	P1.08 / PWM1N / ADC_IN11	I/O	T <sub>T</sub>	x	Х		04	х	х		Port 1.08	PWM: PWM1 complementary output <sup>(8)</sup>	ADC: analog input 11
88	B5	56	B4	P1.07 / PWM2	I/O	T <sub>T</sub>	X	Х	EIT8	04	Х	Х		Port 1.07	PWM: PWM2 out	put <sup>(4)</sup>
89	<b>A</b> 5	57	A4	P1.06 / PWM2N / ADC_IN10	I/O	T <sub>T</sub>	х	х		04	х	х		Port 1.06	PWM: PWM2 complementary output <sup>(4)</sup>	ADC: analog input 10
90	B4	58	ВЗ	P1.05 / PWM3	I/O	T <sub>T</sub>	Х	Х	EIT7	04	Х	Х		Port 1.05	PWM: PWM3 out	put <sup>(4)</sup>

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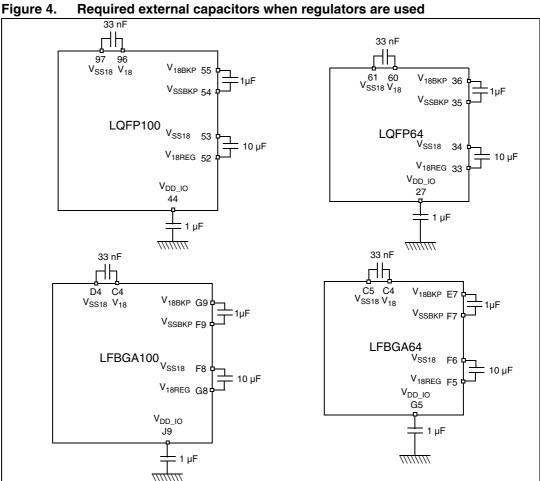
Table 6. STR750F pin description (continued)

	Pin	n°					In	put		C	utpu	ıt	5					
LQFP100 <sup>(1)</sup>	LFBGA100 <sup>(1)</sup>	LQFP64 <sup>(2)</sup>	LFBGA64 <sup>(2)</sup>	Pin name	Туре	Input Level	floating	pd/nd	Ext. int /Wake-up	Capability	OD (3)	PP	Usable in Standby	Main function (after reset)	Alternate	e function		
91	A4	59	АЗ	P1.04 / PWM3N / ADC_IN9	I/O	T <sub>T</sub>	х	Х		04	Х	Х		Port 1.04	PWM: PWM3 complementary output <sup>(4)</sup> ADC: analog input 9			
92	А3			P1.14 / ADC_IN15	I/O	T <sub>T</sub>	х	Х		08	Х	Х		Port 1.14	ADC: analog input 15			
93	A2			P1.13 / ADC_IN14	I/O	T <sub>T</sub>	x	X	EIT13	08	Х	X		Port 1.13	ADC: analog inpu	t 14		
94	D5			P1.01 / TIM0_TI2	I/O	T <sub>T</sub>	x	х		O2	х	х		Port 1.01		TIM0: Input Capture / trigger / external clock 2 (remappable to P0.05) <sup>(8)</sup>		
95	E6			P1.00 / TIM0_OC2	I/O	T <sub>T</sub>	х	Х		02	Х	Х		Port 1.00	TIM0: Output com (remappable to Po			
96	C4	60	C4	V18	S									external capa See <i>Figure 4</i> . To be connec	abilization for main voltage regulator. Requires ternal capacitors 33nF between V18 and VSS18. the Figure 4.2. be connected to the 1.8V external power supply the membedded regulators are not used.			
97	D4	61	C5	VSS18	S									Ground Voltage	Voltage for the main voltage regulator.			
98	D3	62	A2	VSS_IO	S									Ground Voltage	nd Voltage for digital I/Os			
99	СЗ	63	B2	VDD_IO	S									Supply Voltag	ly Voltage for digital I/Os			
100	A1	64	A1	P0.03 / TIM2_TI1 / ADC_IN1	I/O	T <sub>T</sub>	x	х		O2	х	х		Port 0.03	TIM2: Input Capture / trigger / external clock 1	ADC: analog input 1		

- 1. For STR755FVx part numbers, the USB pins must be left unconnected.
- 2. The non available pins on LQPFP64 and LFBGA64 packages are internally tied to low level.
- None of the I/Os are True Open Drain: when configured as Open Drain, there is always a protection diode between the I/O pin and VDD\_IO.
- 4. In the 100-pin package, this Alternate Function is duplicated on two ports. You can configure one port to use this AF, the other port is then free for general purpose I/O (GPIO), external interrupt/wake-up lines, or analog input (ADC\_IN) where these functions are listed in the table.
- 5. It is mandatory that the NJTRST pin is reset to ground during the power-up phase. It is recommended to connect this pin to NRSTOUT pin (if available) or NRSTIN.
- 6. After reset, these pins are enabled as JTAG alternate function see (*Port reset state on page 16*). To use these ports as general purpose I/O (GPIO), the DBGOFF control bit in the GPIO\_REMAPOR register must be set by software (in this case, debugging these I/Os via JTAG is not possible).
- 7. There are two different TQFP and BGA 64-pin packages: in the first one, pins 41 and 42 are mapped to USB DN/DP while for the second one, they are mapped to P0.15/CAN\_TX and P0.14/CAN\_RX.
- 8. For details on remapping these alternate functions, refer to the GPIO\_REMAPOR register description.

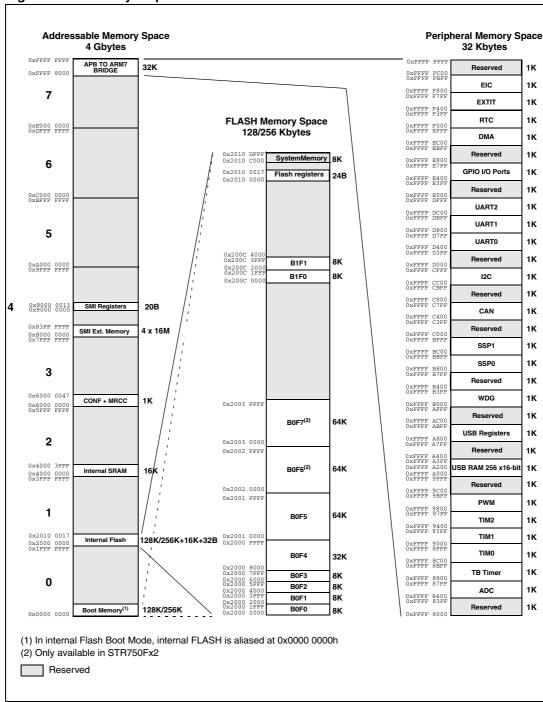
#### 4.2 **External components**

33 nF 97 96 V<sub>SS18</sub> V<sub>18</sub> 61 60 V<sub>SS18</sub> V<sub>18</sub> V<sub>18BKP</sub> 55 V<sub>18BKP</sub> 36 V<sub>SSBKP 54</sub>  $\rm V_{SSBKP~35}$ LQFP64 V<sub>SS18</sub> 34 LQFP100 V<sub>SS18</sub> 53 V<sub>18REG</sub> 52



# 5 Memory map





# 6 Electrical parameters

## 6.1 Parameter conditions

Unless otherwise specified, all voltages are referred to V<sub>SS</sub>.

## 6.1.1 Minimum and maximum values

Unless otherwise specified the minimum and maximum values are guaranteed in the worst conditions of ambient temperature, supply voltage and frequencies by tests in production on 100% of the devices with an ambient temperature at  $T_A$ max (given by the selected temperature range).

Data based on product characterisation, design simulation and/or technology characteristics are indicated in the table footnotes and are not tested in production. Based on characterization, the minimum and maximum values refer to sample tests and represent the mean value plus or minus three times the standard deviation (mean $\pm 3\Sigma$ ).

## 6.1.2 Typical values

Unless otherwise specified, typical data are based on  $T_A=25^{\circ}$  C,  $V_{DD\_IO}=3.3$  V (for the 3.0 V $\leq$ V $_{DD\_IO}\leq$ 3.6 V voltage range) and V $_{18}=1.8$  V. They are given only as design guidelines and are not tested.

Typical ADC accuracy values are determined by characterization of a batch of samples from a standard diffusion lot over the full temperature range, where 95% of the devices have an error less than or equal to the value indicated (mean $\pm 2\Sigma$ ).

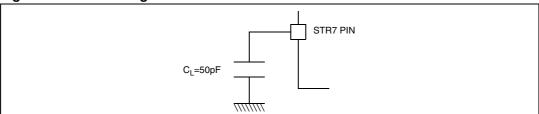
## 6.1.3 Typical curves

Unless otherwise specified, all typical curves are given only as design guidelines and are not tested.

# 6.1.4 Loading capacitor

The loading conditions used for pin parameter measurement are shown in *Figure 6*.

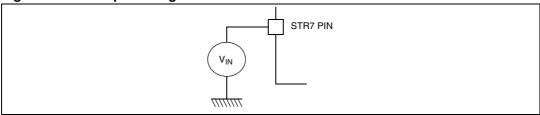
Figure 6. Pin loading conditions



# 6.1.5 Pin input voltage

The input voltage measurement on a pin of the device is described in *Figure 7*.

Figure 7. Pin input voltage

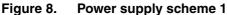


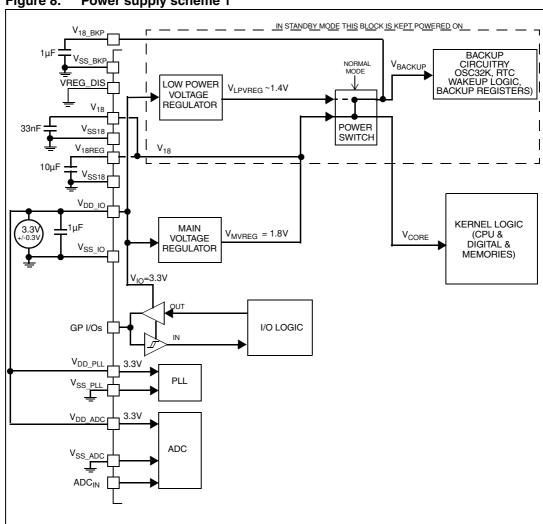
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## 6.1.6 Power supply schemes

When mentioned, some electrical parameters can refer to a dedicated power scheme among the four possibilities. The four different power schemes are described below.

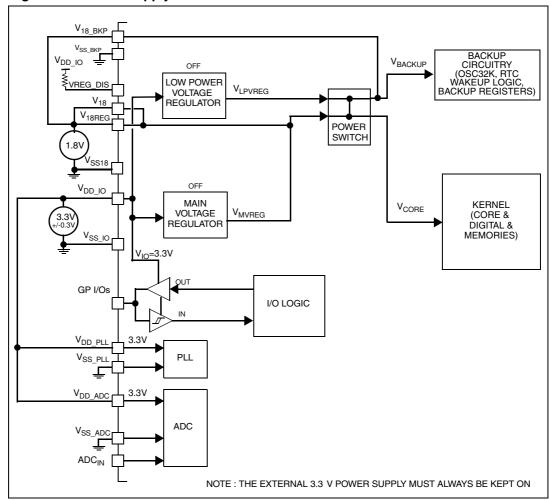
## Power supply scheme 1: Single external 3.3 V power source





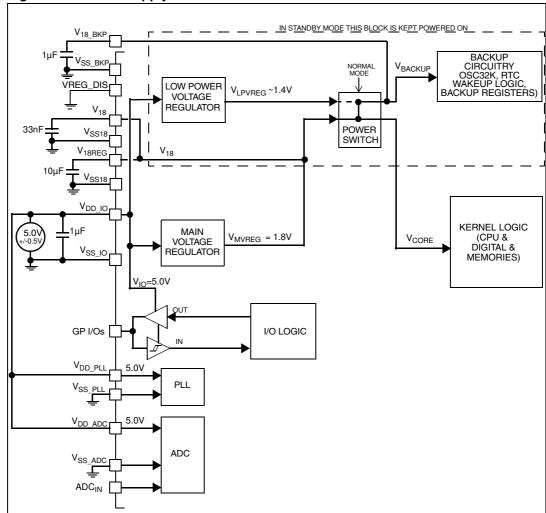
# Power supply scheme 2: Dual external 1.8V and 3.3V supply

Figure 9. Power supply scheme 2



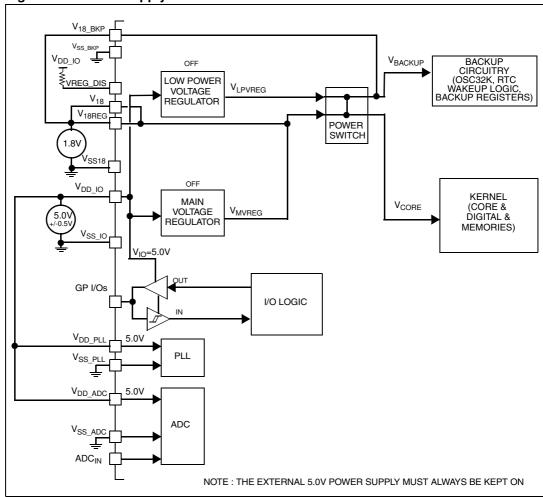
## Power supply scheme 3: Single external 5 V power source

Figure 10. Power supply scheme 3



## Power supply scheme 4: Dual external 1.8 V and 5.0 V supply

Figure 11. Power supply scheme 4



## 6.1.7 I/O characteristics versus the various power schemes (3.3V or 5.0V)

Unless otherwise mentioned, all the I/O characteristics are valid for both

- V<sub>DD IO</sub>=3.0 V to 3.6 V with bit EN33=1
- V<sub>DD IO</sub>=4.5 V to 5.5 V with bit EN33=0

When  $V_{DD\ IO}$ =3.0 V to 3.6 V, I/Os are not 5V tolerant.

## 6.1.8 Current consumption measurements

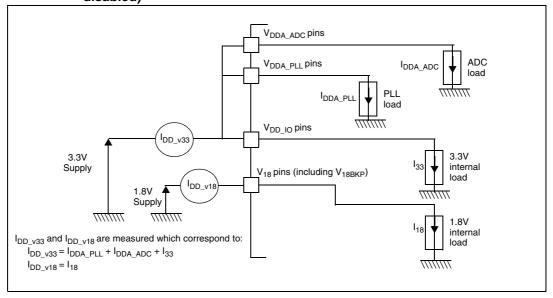
All the current consumption measurements mentioned below refer to Power scheme 1 and 2 as described in *Figure 12* and *Figure 13* 

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V<sub>DDA\_ADC</sub> pins ADC  $V_{DDA\_PLL}$  pins load I<sub>DDA\_PLL</sub> mm $V_{DD\_IO}$  pins  $\mathsf{I}_{\mathsf{DD}}$ ballast regulator I<sub>33</sub> transistor 3.3V 3.3V internal Supply load  $\overline{V}_{18}$  pins (including  $V_{18BKP}$ ) 11111111 1.8V internal load  $I_{\mbox{\scriptsize DD}}$  is measured, which corresponds to the total current consumption :  $I_{DD} = I_{DDA\_PLL} + I_{DDA\_ADC} + I_{33} + I_{18}$ 

Figure 12. Power consumption measurements in power scheme 1 (regulators enabled)

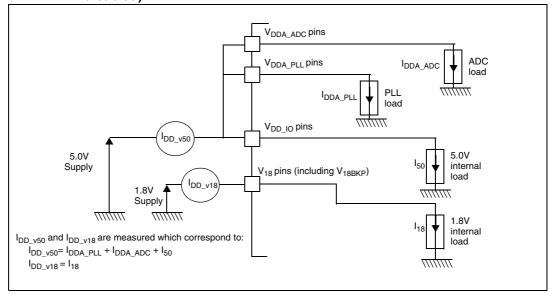
Figure 13. Power consumption measurements in power scheme 2 (regulators disabled)



V<sub>DDA\_ADC</sub> pins ADC  $V_{DDA\_PLL}$  pins load I<sub>DDA\_PLL</sub> mm $V_{DD\_IO}$  pins  $\mathsf{I}_{\mathsf{DD}}$ ballast regulator I<sub>50</sub> transistor 5.0V 5.0V internal Supply load  $\overline{V}_{18}$  pins (including  $V_{18BKP}$ ) 11111111 1.8V internal load  $I_{\mbox{\scriptsize DD}}$  is measured, which corresponds to the total current consumption :  $I_{DD} = I_{DDA\_PLL} + I_{DDA\_ADC} + I_{50} + I_{18}$ 

Figure 14. Power consumption measurements in power scheme 3 (regulators enabled)

Figure 15. Power consumption measurements in power scheme 4 (regulators disabled)



# 6.2 Absolute maximum ratings

Stresses above those listed as "absolute maximum ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device under these conditions is not implied. Exposure to maximum rating conditions for extended periods may affect device reliability.

## 6.2.1 Voltage characteristics

Table 7. Voltage characteristics

Symbol	Ratings	Min	Max	Unit
$V_{DD_x} - V_{SS_x}^{(1)}$	Including $V_{DDA\_ADC}$ and $V_{DDA\_PLL}$	-0.3	6.5	V
V <sub>18</sub> - V <sub>SS18</sub>	Digital 1.8 V Supply voltage on all V <sub>18</sub> power pins (when 1.8 V is provided externally)	-0.3	2.0	
V <sub>IN</sub>	Input voltage on any pin <sup>(2)</sup>	V <sub>SS</sub> -0.3 to V <sub>DD_IO</sub> +0.3	$V_{SS}$ -0.3 to $V_{DD\_IO}$ +0.3	
IΔV <sub>DDx</sub> I	Variations between different 3.3 V or 5.0 V power pins		50	
l∆V <sub>18x</sub> l	Variations between different 1.8 V power pins <sup>(3)</sup>		25	mV
IV <sub>SSX</sub> - V <sub>SS</sub> I	Variations between all the different ground pins		50	
V <sub>ESD(HBM)</sub>	Electro-static discharge voltage (Human Body Model)	see : Absolute maximum	see : Absolute maximum	
V <sub>ESD(MM)</sub>	Electro-static discharge voltage (Machine Model)	ratings (electrical sensitivity) on page 52	ratings (electrical sensitivity) on page 52	

All 3.3 V or 5.0 V power (V<sub>DD\_IO</sub>, V<sub>DDA\_ADC</sub>, V<sub>DDA\_PLL</sub>) and ground (V<sub>SS\_IO</sub>, V<sub>SSA\_ADC</sub>, V<sub>DDA\_ADC</sub>) pins must always be connected to the external 3.3V or 5.0V supply. When powered by 3.3V, I/Os are not 5V tolerant

I<sub>INJ(PIN)</sub> must never be exceeded. This is implicitly insured if V<sub>IN</sub> maximum is respected. If V<sub>IN</sub> maximum cannot be respected, the injection current must be limited externally to the I<sub>INJ(PIN)</sub> value. A positive injection is induced by V<sub>IN</sub>>V<sub>DD</sub> while a negative injection is induced by V<sub>IN</sub><V<sub>SS</sub>. For true open-drain pads, there is no positive injection current, and the corresponding V<sub>IN</sub> maximum must always be respected

Only when using external 1.8 V power supply. All the power (V<sub>18</sub>, V<sub>18REG</sub>, V<sub>18BKP</sub>) and ground (V<sub>SS18</sub>, V<sub>SSBKP</sub>) pins must always be connected to the external 1.8 V supply.

#### 6.2.2 Current characteristics

Table 8. Current characteristics

Symbol	Ratings	Maximum value	Unit
I <sub>VDD_IO</sub> <sup>(1)</sup>	Total current into V <sub>DD_IO</sub> power lines (source) (2)	150	
I <sub>VSS_IO</sub> <sup>(1)</sup>	Total current out of V <sub>SS</sub> ground lines (sink) (2)	150	
1.	Output current sunk by any I/O and control pin	25	
I <sub>IO</sub>	Output current source by any I/Os and control pin	- 25	mA
	Injected current on NRSTIN pin	± 5	ША
I <sub>INJ(PIN)</sub> (3) & (4)	Injected current on XT1 and XT2 pins	± 5	
	Injected current on any other pin (5)	± 5	
$\Sigma I_{\text{INJ(PIN)}}^{(3)}$	Total injected current (sum of all I/O and control pins) (5)	± 25	

- 1. The user can use GPIOs to source or sink high current (up to 20 mA for O8 type High Sink I/Os). In this case, the user must ensure that these absolute max. values are not exceeded (taking into account the RUN power consumption) and must follow the rules described in Section 6.3.8: I/O port pin characteristics on page 54.
- 2. All 3.3 V or 5.0 V power ( $V_{DD\_IO}$ ,  $V_{DDA\_ADC}$ ,  $V_{DDA\_PLL}$ ) and ground ( $V_{SS\_IO}$ ,  $V_{SSA\_ADC}$ ,  $V_{DDA\_ADC}$ ) pins must always be connected to the external 3.3V or 5.0V supply.
- 3.  $I_{INJ(PIN)}$  must never be exceeded. This is implicitly insured if  $V_{IN}$  maximum is respected. If  $V_{IN}$  maximum cannot be respected, the injection current must be limited externally to the  $I_{INJ(PIN)}$  value. A positive injection is induced by  $V_{IN} > V_{DD}$  while a negative injection is induced by  $V_{IN} < V_{SS}$ . Data based on  $T_A = 25$ °C.
- 4. Negative injection disturbs the analog performance of the device. See note in Section 6.3.12: 10-bit ADC characteristics on page 72.
- 5. When several inputs are submitted to a current injection, the maximum ΣI<sub>INJ(PIN)</sub> is the absolute sum of the positive and negative injected currents (instantaneous values). These results are based on characterization with ΣI<sub>INJ(PIN)</sub> maximum current injection on four I/O port pins of the device.

#### 6.2.3 Thermal characteristics

Table 9. Thermal characteristics

Symbol	Ratings	Value	Unit	
T <sub>STG</sub>	Storage temperature range	-65 to +150	°C	
T <sub>J</sub>	Maximum junction temperature	150	°C	

# 6.3 Operating conditions

## 6.3.1 General operating conditions

Subject to general operating conditions for  $V_{DD\ IO}$ , and  $T_A$  unless otherwise specified.

Table 10. General operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit		
		Accessing SRAM with 0 wait states	0	64			
		Accessing Flash in burst mode, T <sub>A</sub> ≤85° C	0	60			
f <sub>HCLK</sub>	Internal AHB Clock frequency	Accessing Flash in burst mode T <sub>A</sub> >85° C		56	MHz		
		Accessing Flash with 0 wait states	0	32	IVII IZ		
		Write access to Flash registers <sup>(1)</sup>	0	30			
		Accessing Flash in RWW mode	0	16			
f <sub>PCLK</sub>	Internal APB Clock frequency		0	32	MHz		
N/	Standard Operating Voltage Power Scheme 1 & 2		3.0	3.6			
V <sub>DD_IO</sub>	Standard Operating Voltage Power Scheme 3 & 4		4.5	5.5	٧		
V <sub>18</sub>	Standard Operating Voltage Power Scheme 2 & 4		1.65	1.95			
		LQFP100		434			
	Power dissipation at T <sub>A</sub> = 85° C	LQFP64		444			
P <sub>D</sub>	for suffix 6 or $T_A = 105^{\circ}$ C for suffix $7^{(2)}$	LFBGA100		487	mW		
		LFBGA64		344			
	Ambient temperature for 6 suffix	Maximum power dissipation	-40	85	°C		
T <sub>A</sub>	version	Low power dissipation <sup>(3)</sup>	-40	105	°C		
'A	Ambient temperature for 7 suffix	Maximum power dissipation	-40	105	°C		
	version	Low power dissipation (3)	-40	125	°C		
TJ	Junction temperature range	6 Suffix Version	-40	105	°C		
' J	danotion temperature range	7 Suffix Version	-40	125	°C		

<sup>1.</sup> Write access to Flash registers is either a program, erase, set protection or un-set protection operation.

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If T<sub>A</sub> is lower, higher PD values are allowed as long as T<sub>J</sub> does not exceed T<sub>Jmax</sub> (see Section 7.2: Thermal characteristics on page 79).

<sup>3.</sup> In low power dissipation state,  $T_A$  can be extended to this range as long as  $T_J$  does not exceed  $T_{Jmax}$  (see Section 7.2: Thermal characteristics on page 79).

#### 6.3.2 Operating conditions at power-up / power-down

Subject to general operating conditions for T<sub>A</sub>.

Table 11. Operating conditions at power-up / power-down

Symbol	Parameter	Conditions	Min <sup>(1)</sup>	Тур	Max <sup>(1)</sup>	Unit
t	V <sub>DD IO</sub> rise time rate		20			μs/V
t <sub>VDD</sub> IO	VDD_IO rise time rate				20	ms/V
t <sub>V18</sub>	V <sub>18</sub> rise time rate <sup>(1)</sup>	When 1.8 V power is supplied	20			μs/V
	V <sub>18</sub> rise time rate · ·	externally			20	ms/V

<sup>1.</sup> Data guaranteed by characterization, not tested in production.

#### 6.3.3 **Embedded voltage regulators**

Subject to general operating conditions for  $V_{DD\ IO}$ , and  $T_A$ 

Table 12. **Embedded voltage regulators** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>MVREG</sub>	MVREG power supply <sup>(1)</sup>	load <150 mA	1.65	1.80	1.95	V
V <sub>LPVREG</sub>	LPVREG power supply <sup>(2)</sup>	load <10 mA	1.30	1.40	1.50	V
t (1)	Voltage Regulators start-up	V <sub>DD_IO</sub> rise slope = 20 μs/V		80		μs
t <sub>VREG_PWRUP</sub> <sup>(1)</sup>	time (to reach 90% of final V <sub>18</sub> value) at V <sub>DD_IO</sub> power-up <sup>(3)</sup>	V <sub>DD_IO</sub> rise slope = 20 ms/V		35		ms

 $V_{MVREG}$  is observed on the  $V_{18},\,V_{18REG}$  and  $V_{18BKP}$  pins except in the following case: - In STOP mode with MVREG OFF (LP\_PARAM13 bit). See note 2. - In STANDBY mo*de. See note 2.* 

<sup>2.</sup> In STANDBY mode,  $V_{LPVREG}$  is observed on the  $V_{18BKP}$  pin In STOP mode,  $V_{LPVREG}$  is observed on the  $V_{18}$ ,  $V_{18REG}$  and  $V_{18BKP}$  pins.

<sup>3.</sup> Once  $V_{DD\_IO}$  has reached 3.0 V, the RSM (Regulator Startup Monitor) generates an internal RESET during this start-up time.

## 6.3.4 Supply current characteristics

The current consumption is measured as described in *Figure 12 on page 30* and *Figure 13 on page 30*.

Subject to general operating conditions for  $V_{DD\ IO}$ , and  $T_A$ 

## **Maximum power consumption**

For the measurements in *Table 13* and *Table 14*, the MCU is placed under the following conditions:

- All I/O pins are configured in output push-pull 0
- All peripherals are disabled except if explicitly mentioned.
- Embedded Regulators are used to provide 1.8 V (except if explicitly mentioned).

Table 13. Maximum power consumption in RUN and WFI modes

Symbol	Parameter	Conditions <sup>(1)</sup>		Typ <sup>(2)</sup>	Max <sup>(3)</sup>	Unit
I <sub>DD</sub>	Supply current in RUN mode	External Clock with PLL multiplication, code running from RAM, all peripherals enabled in the MRCC_PLCKEN register: f <sub>HCLK</sub> =60 MHz, f <sub>PCLK</sub> =30 MHz Single supply scheme see <i>Figure 12</i> / <i>Figure 14</i>	3.3V and 5V range	80	90	mA
55	Supply current in WFI mode	External Clock, code running from RAM: f <sub>HCLK</sub> =60 MHz, f <sub>PCLK</sub> =30 MHz Single supply scheme see <i>Figure 12./ Figure 14</i> Parameter setting BURST=1, WFI_FLASHEN=1	3.3V and 5V range	62	67	mA

- 1. The conditions for these consumption measurements are described at the beginning of Section 6.3.4.
- 2. Typical data are based on  $T_A$ =25°C,  $V_{DD\ IO}$ =3.3V or 5.0V and  $V_{18}$ =1.8V unless otherwise specified.
- 3. Data based on product characterisation, tested in production at  $V_{DD\_IO}$  max and  $V_{18}$  max (1.95V in dual supply mode or regulator output value in single supply mode) and  $T_A$  max.

Table 14. Maximum power consumption in STOP and STANDBY modes

		Conditions <sup>(1)</sup>			Max <sup>(3)</sup>			
Symbol	Parameter			Typ <sup>(2)</sup>	T <sub>A</sub> 25°C	T <sub>A</sub> 85°C	T <sub>A</sub> 105°C	Unit
		LP_PARAM bits: ALL OFF <sup>(4)</sup> Single supply scheme see <i>Figure 12</i> .	3.3V range	12	16	117	250	μΑ
Supply	Supply current in	LP_PARAM bits: ALL OFF Dual supply scheme see Figure 13.	I <sub>DD_V18</sub> I <sub>DD_V33</sub>	5 <1	8 3	60 20	110 26	μΑ
I <sub>DD</sub>	STOP mode	LP_PARAM bits: ALL OFF <sup>(4)</sup> Single supply scheme see <i>Figure 10</i>	5V range	15	22	160	310	μΑ
.00		LP_PARAM bits: ALL OFF Dual supply scheme see Figure 11	I <sub>DD_V18</sub> I <sub>DD_V50</sub>	5 3	8 6	60 50	110 65	
	Supply current in	RTC OFF	3.3 V range	10	20	25	28	μΑ
	STANDBY mode		5V range	15	25	30	33	

<sup>1.</sup> The conditions for these consumption measurements are described at the beginning of Section 6.3.4.

<sup>2.</sup> Typical data are based on  $T_A$ =25°C,  $V_{DD\_IO}$ =3.3V or 5.0V and  $V_{18}$ =1.8V unless otherwise specified.

<sup>3.</sup> Data based on product characterisation, tested in production at  $V_{DD\_IO}$  max and  $V_{18}$  max (1.95V in dual supply mode or regulator output value in single supply mode).

<sup>4.</sup> In this mode, the whole digital circuitry is powered internally by the LPVREG at approximately 1.4V, which significantly reduces the leakage currents.

Figure 16. Power consumption in STOP mode in Single supply scheme (3.3 V range)

Power consumption in STOP mode Single supply scheme (5 V range)

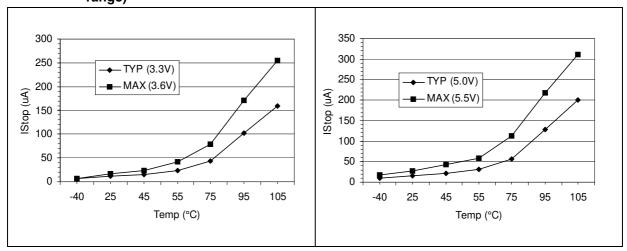
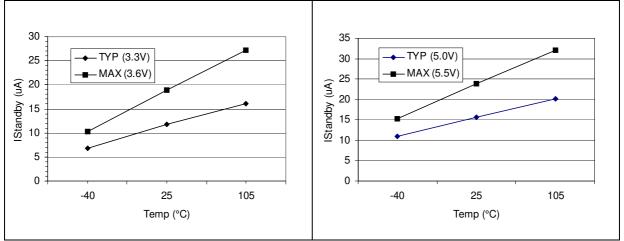


Figure 18. Power consumption in STANDBY mode (3.3 V range)

Figure 19. Power consumption in STANDBY mode (5 V range)



## **Typical power consumption**

The following measurement conditions apply to Table 15, Table 16 and Table 17.

#### In RUN mode:

- Program is executed from Flash (except if especially mentioned). The program consists of an infinite loop. When f<sub>HCL K</sub> > 32 MHz, burst mode is activated.
- A standard 4 MHz crystal source is used.
- In all cases the PLL is used to multiply the frequency.
- All measurements are done in the single supply scheme with internal regulators used (see Figure 12)

### In WFI Mode:

- In WFI Mode the measurement conditions are similar to RUN mode (OSC4M and PLL enabled). In addition, the Flash can be disabled depending on burst mode activation:
  - For AHB frequencies greater than 32 MHz, burst mode is activated and the Flash is kept enabled by setting the WFI\_FLASH\_EN bit (this bit cannot be reset when burst mode is activated).
  - For AHB frequencies less than or equal to 32 MHz, burst mode is deactivated, WFI\_FLASH\_EN is reset and the LP\_PARAM14 bit is set (Flash is disabled in WFI mode).

#### In SLOW mode:

 The same program as in RUN mode is executed from Flash. The CPU is clocked by the FREEOSC, OSC4M, LPOSC or OSC32K. Only EXTIT peripheral is enabled in the MRCC\_PCLKEN register.

### In SLOW-WFI mode:

 In SLOW-WFI, the measurement conditions are similar to SLOW mode (CPU clocked by a low frequency clock). In addition, the LP\_PARAM14 bit is set (FLASH is OFF). The WFI routine itself is executed from SRAM (it is not allowed to execute a WFI from the internal FLASH)

#### In STOP mode:

• Several measurements are given: in the single supply scheme with internal regulators used (see *Figure 12*): and in the dual supply scheme (see *Figure 13*).

#### In STANDBY mode:

- Three measurements are given:
  - The RTC is disabled, only the consumption of the LPVREG and RSM remain (almost no leakage currents)
  - The RTC is running, clocked by a standard 32.768 kHz crystal.
  - The RTC is running, clocked by the internal Low Power RC oscillator (LPOSC)
- STANDBY mode is only supported in the single supply scheme (see Figure 12)

Subject to general operating conditions for  $V_{DD\_IO},$  and  $T_{A}$ 

Table 15. Single supply typical power consumption in Run, WFI, Slow and Slow-WFI modes

Symbol	Para meter	Conditions	3.3V typ <sup>(1)</sup>	5V typ <sup>(2)</sup>	Unit
	Supply current in	Clocked by OSC4M with PLL multiplication, all peripherals enabled in the MRCC_PLCKEN register: $f_{HCLK}=60 \text{ MHz}, f_{PCLK}=30 \text{ MHz} \\ f_{HCLK}=56 \text{ MHz}, f_{PCLK}=28 \text{ MHz} \\ f_{HCLK}=48 \text{ MHz}, f_{PCLK}=24 \text{ MHz} \\ f_{HCLK}=32 \text{ MHz}, f_{PCLK}=32 \text{ MHz} \\ f_{HCLK}=16 \text{ MHz}, f_{PCLK}=16 \text{ MHz} \\ f_{HCLK}=8 \text{ MHz}, f_{PCLK}=8 \text{ MHz}$	80 75 65 59 34 20	82 77 67 61 37 22	mA
(3)	RUN mode <sup>(4)</sup>	Clocked by OSC4M with PLL multiplication, only EXTIT peripheral enabled in the MRCC_PLCKEN register: $f_{HCLK}=60 \text{ MHz}, f_{PCLK}=30 \text{ MHz}$ $f_{HCLK}=56 \text{ MHz}, f_{PCLK}=28 \text{ MHz}$ $f_{HCLK}=48 \text{ MHz}, f_{PCLK}=24 \text{ MHz}$ $f_{HCLK}=32 \text{ MHz}, f_{PCLK}=32 \text{ MHz}$ $f_{HCLK}=36 \text{ MHz}, f_{PCLK}=16 \text{ MHz}$ $f_{HCLK}=8 \text{ MHz}, f_{PCLK}=8 \text{ MHz}$	65 60 54 42 22 16	67 62 55 44 24 18	mA
I <sub>DD</sub> <sup>(3)</sup>	Supply current in WFI mode <sup>(4)</sup>	Clocked by OSC4M with PLL multiplication, only EXTIT peripheral enabled in the MRCC_PLCKEN register: $      f_{\text{HCLK}} = 60 \text{ MHz}, f_{\text{PCLK}} = 30 \text{ MHz}^{(5)} $ $      f_{\text{HCLK}} = 56 \text{ MHz}, f_{\text{PCLK}} = 28 \text{ MHz}^{(5)} $ $      f_{\text{HCLK}} = 48 \text{ MHz}, f_{\text{PCLK}} = 24 \text{ MHz}^{(5)} $ $      f_{\text{HCLK}} = 32 \text{ MHz}, f_{\text{PCLK}} = 32 \text{ MHz}^{(6)} $ $      f_{\text{HCLK}} = 16 \text{ MHz}, f_{\text{PCLK}} = 16 \text{ MHz}^{(6)} $ $      f_{\text{HCLK}} = 8 \text{ MHz}, f_{\text{PCLK}} = 8 \text{ MHz}^{(6)} $	62 59 53 22 13	63 60 54 23 15	mA
	Supply current in SLOW mode <sup>(4)</sup>	Clocked by FREEOSC: f <sub>HCLK</sub> =f <sub>PCLK</sub> =~5 MHz, Clocked by OSC4M: f <sub>HCLK</sub> =f <sub>PCLK</sub> =4 MHz Clocked by LPOSC: f <sub>HCLK</sub> =f <sub>PCLK</sub> =~300 kHz Clocked by OSC32K: f <sub>HCLK</sub> =f <sub>PCLK</sub> =32.768 kHz	9 8 3.65 3.5	10 9 3.9 4.2	mA
	Supply current in SLOW-WFI mode <sup>(4)(7)</sup>	Clocked by FREEOSC: f <sub>HCLK</sub> =f <sub>PCLK</sub> =~5 MHz Clocked by OSC4M: f <sub>HCLK</sub> =f <sub>PCLK</sub> =4 MHz Clocked by LPOSC: f <sub>HCLK</sub> =f <sub>PCLK</sub> =~300 kHz Clocked by OSC32K: f <sub>HCLK</sub> =f <sub>PCLK</sub> =32.768 kHz	3.5 3.1 1.15 0.98	4.0 3.75 1.65 1.5	mA

<sup>1.</sup> Typical data based on  $T_A \!\!=\!\! 25^\circ$  C and  $V_{DD\_IO} \!\!=\!\! 3.3 V.$ 

<sup>2.</sup> Typical data based on  $T_A \! = \! 25^{\circ}$  C and  $V_{DD\_IO} \! = \! 5.0 V.$ 

<sup>3.</sup> The conditions for these consumption measurements are described at the beginning of Section 6.3.4 on page 36.

<sup>4.</sup> Single supply scheme see *Figure 14*.

<sup>5.</sup> Parameter setting BURST=1, WFI\_FLASHEN=1

<sup>6.</sup> Parameter setting BURST=0, WFI\_FLASHEN=0

<sup>7.</sup> Parameter setting WFI\_FLASHEN=0, OSC4MOFF=1

Table 16. Dual supply supply typical power consumption in Run, WFI, Slow and Slow-WFI modes

To calculate the power consumption in Dual supply mode, refer to the values given in *Table 15*. and consider that this consumption is split as follows:

 $I_{DD(\text{single supply})} \sim I_{DD(\text{dual supply})} = I_{DD_V18} + I_{DD(VDD_IO)}$ 

For 3.3V range:  $I_{DD(VDD\_IO)} \sim 1$  to 2 mA For 5V range:  $I_{DD(VDD\_IO)} \sim 2$  to 3 mA

Therefore most of the consumption is sunk on the V<sub>18</sub> power supply

This formula does not apply in STOP and STANDBY modes, refer to Table 17.

Subject to general operating conditions for  $V_{DD\_IO}$ , and  $T_A$ 

Table 17. Typical power consumption in STOP and STANDBY modes

Symbol	Parameter	Conditions		3.3V Typ <sup>(1)</sup>	5V Typ <sup>(2)</sup>	Unit	
		LP_PARAM bits: ALL OFF <sup>(5)</sup>		12	15		
	Supply current	LP_PARAM bits : MVREG ON, OSC4M OFF, F	LASH	130	135		
	in STOP mode <sup>(4)</sup>	LP_PARAM bits: MVREG ON, OSC4M ON , FI $OFF^{(6)}$	_ASH	1950	1930	μА	
		LP_PARAM bits: MVREG ON, OSC4M OFF, FLASH ON (6)		630	635	1	
		LP_PARAM bits: MVREG ON, OSC4M ON, FLASH ON (6)			2425		
I <sub>DD</sub> <sup>(3)</sup>	Supply current in STOP	LPPARAM bits: ALL OFF, with V <sub>18</sub> =1.8 V	I <sub>DD_V18</sub> I <sub>DD_V33</sub>	5 <1	5 <1		
		LP_PARAM bits: OSC4M ON, FLASH OFF	I <sub>DD_V18</sub> I <sub>DD_V33</sub>	410 1475	410 1435	μА	
	mode <sup>(7)</sup>	LP_PARAM bits: OSC4M OFF, FLASH ON	I <sub>DD_V18</sub> I <sub>DD_V33</sub>	550 <1	550 1	μΑ	
		LP_PARAM bits: OSC4M ON, FLASH ON	I <sub>DD_V18</sub> I <sub>DD_V33</sub>	910 1475	910 1445		
	Supply current	RTC OFF		11	14		
in STANDBY mode <sup>(4)</sup>		RTC ON clocked by OSC32K		14	18	μА	

- 1. Typical data are based on  $T_A=25^{\circ}C$ ,  $V_{DD\ IO}=3.3\ V$  and  $V_{18}=1.8\ V$  unless otherwise indicated in the table.
- 2. Typical data are based on  $T_A$ =25°C,  $V_{DD\ IO}$ =5.0 V and  $V_{18}$ =1.8 V unless otherwise indicated in the table.
- 3. The conditions for these consumption measurements are described at the beginning of Section 6.3.4 on page 36.
- 4. Single supply scheme see Figure 12.
- In this mode, the whole digital circuitry is powered internally by the LPVREG at approximately 1.4 V, which significantly reduces the leakage currents.
- 6. In this mode, the whole digital circuitry is powered internally by the MVREG at 1.8 V.
- 7. Dual supply scheme see Figure 13.

# Supply and clock manager power consumption

Table 18. Supply and clock manager power consumption

Symbol	Parameter	Conditions <sup>(1)</sup>	3.3V Typ	5V Typ	Unit
I <sub>DD(OSC4M)</sub>	Supply current of resonator oscillator in STOP or WFI mode (LP_PARAM bit: OSC4M ON)	External components specified in: 4/8 MHz crystal / ceramic resonator oscillator (XT1/XT2) on page 46	1815	1795	
I <sub>DD(FLASH)</sub>	FLASH static current consumption in STOP or WFI mode (LP_PARAM bit FLASH ON)		515	515	
I <sub>DD(MVREG)</sub>	Main Voltage Regulator static current consumption in STOP mode (LP_PARAM bit: MVREG ON)		130	135	μΑ
	Low Power Voltage Regulator + RSM	STOP mode includes leakage where V <sub>18</sub> is internally set to 1.4 V	12	15	
I <sub>DD(LPVREG)</sub>	current static current consumption	STANDBY mode where V <sub>18BKP</sub> and V <sub>18</sub> are internally set to 1.4 V and 0 V respectively	11	14	

<sup>1.</sup> Measurements performed in 3.3V single supply mode see *Figure 12* 

# On-Chip peripheral power consumption

#### **Conditions:**

- VDD\_IO=VDDA\_ADC=VDDA\_PLL=3.3 V or 5 V  $\pm 10\%$  unless otherwise specified.
- $T_A = 25^{\circ} C$
- Clocked by OSC4M with PLL multiplication,  $f_{CK\_SYS}$ =64 MHz,  $f_{HCLK}$ =32 MHz,  $f_{PCLK}$ =32 MHz

Table 19. On-Chip peripherals

Symbol	Parameter	Typ (3.3V and 5.0V)	Unit
I <sub>DD(TIM)</sub>	TIM Timer supply current (1)	0.7	
I <sub>DD(PWM)</sub>	PWM Timer supply current <sup>(2)</sup>	1	
I <sub>DD(SSP)</sub>	SSP supply current (3)	1.3	
I <sub>DD(UART)</sub>	UART supply current (4)	1.6	
I <sub>DD(I2C)</sub>	I2C supply current <sup>(5)</sup>	0.3	mA
I <sub>DD(ADC)</sub>	ADC supply current when converting <sup>(6)</sup>	1.2	
I <sub>DD(USB)</sub>	USB supply current <sup>(7)</sup> <b>Note:</b> V <sub>DD_IO</sub> must be 3.3 V ±10%	0.90	
I <sub>DD(CAN)</sub>	CAN supply current <sup>(8)</sup>	2.8	

- Data based on a differential I<sub>DD</sub> measurement between reset configuration and timer counter running at 32 MHz. No IC/OC programmed (no I/O pads toggling)
- Data based on a differential I<sub>DD</sub> measurement between reset configuration and PWM running at 32 MHz. This measurement does not include PWM pads toggling consumption.
- Data based on a differential I<sub>DD</sub> measurement between reset configuration and permanent SPI master communication at maximum speed 16 MHz. The data sent is 55h. This measurement does not include the pad toggling consumption.
- Data based on a differential I<sub>DD</sub> measurement between reset configuration and a permanent UART data transmit sequence at 1Mbauds. This measurement does not include the pad toggling consumption.
- Data based on a differential I<sub>DD</sub> measurement between reset configuration (I2C disabled) and a permanent I2C master communication at 100kHz (data sent equal to 55h). This measurement includes the pad toggling consumption but not the external 10kOhm external pull-up on clock and data lines.
- Data based on a differential I<sub>DD</sub> measurement between reset configuration and continuous A/D conversions at 8 MHz in scan mode on 16 inputs configured as AIN.
- Data based on a differential I<sub>DD</sub> measurement between reset configuration and a running generic HID application.
- 8. Data based on a differential IDD measurement between reset configuration (CAN disabled) and a permanent CAN data transmit sequence in loopback mode at 1MHz. This measurement does not include the pad toggling consumption.

# 6.3.5 Clock and timing characteristics

# XT1 external clock source

Subject to general operating conditions for  $V_{DD\_IO}\!,$  and  $T_A\!.$ 

Table 20. XT1 external clock source

Symbol	Parameter	Conditions <sup>(1) (2)</sup>	Min	Тур	Max	Unit
f <sub>XT1</sub>	External clock source frequency			4	60	MHz
V <sub>XT1H</sub>	XT1 input pin high level voltage		0.7xV <sub>DD_IO</sub>		$V_{DD\_IO}$	<b>V</b>
V <sub>XT1L</sub>	XT1 input pin low level voltage	see <i>Figure 20</i>	V <sub>SS</sub>		0.3xV <sub>DD_IO</sub>	V
t <sub>w(XT1H)</sub> t <sub>w(XT1L)</sub>	XT1 high or low time (3)		6			ns
$\begin{array}{c} t_{r(XT1)} \\ t_{f(XT1)} \end{array}$	XT1 rise or fall time (3)				20	115
IL	XTx Input leakage current	$V_{SS} \le V_{IN} \le V_{DD\_IO}$			±1	μА
C <sub>IN(XT1)</sub>	XT1 input capacitance <sup>(3)</sup>			5	_	pF
DuCy <sub>(XT1)</sub>	Duty cycle		45		55	%

<sup>1.</sup> Data based on typical application software.

<sup>2.</sup> Time measured between interrupt event and interrupt vector fetch.  $\Delta t_{c(INST)}$  is the number of  $t_{CPU}$  cycles needed to finish the current instruction execution.

<sup>3.</sup> Data based on design simulation and/or technology characteristics, not tested in production.

## XRTC1 external clock source

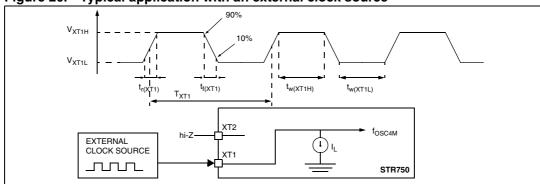
Subject to general operating conditions for  $V_{\mbox{\scriptsize DD\_IO}},$  and  $T_{\mbox{\scriptsize A}}.$ 

Table 21. XRTC1 external clock source

Symbol	Parameter	Conditions <sup>(1)</sup>	Min	Тур	Max	Unit
f <sub>XRTC1</sub>	External clock source frequency			32.768	500	kHz
V <sub>XRTC1H</sub>	XRTC1 input pin high level voltage		0.7xV <sub>DD_IO</sub>		$V_{DD\_IO}$	V
V <sub>XRTC1L</sub>	XRTC1 input pin low level voltage	see <i>Figure 20</i>	V <sub>SS</sub>		0.3xV <sub>DD_IO</sub>	V
t <sub>w(XRTC1H)</sub> t <sub>w(XRTC1L)</sub>	XRTC1 high or low time <sup>(2)</sup>		900			ns
t <sub>r(XRTC1)</sub> t <sub>f(XRTC1)</sub>	XRTC1 rise or fall time <sup>(2)</sup>				50	115
IL	XRTCx Input leakage current	$V_{SS} \le V_{IN} \le V_{DD\_I}$			±1	μА
C <sub>IN(RTC1)</sub>	XRTC1 input capacitance <sup>(2)</sup>			5		pF
DuCy <sub>(RTC1)</sub>	Duty cycle		30		70	%

- 1. Data based on typical application software.
- 2. Data based on design simulation and/or technology characteristics, not tested in production.

Figure 20. Typical application with an external clock source



## 4/8 MHz crystal / ceramic resonator oscillator (XT1/XT2)

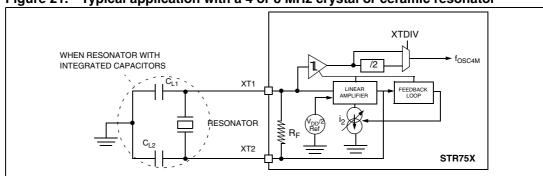
The STR750 system clock or the input of the PLL can be supplied by a OSC4M which is a 4 MHz clock generated from a 4 MHz or 8 MHz crystal or ceramic resonator. If using an 8 MHz oscillator, software set the XTDIV bit to enable a divider by 2 and generate a 4 MHz OSC4M clock. All the information given in this paragraph are based on product characterisation with specified typical external components. In the application, the resonator and the load capacitors have to be placed as close as possible to the oscillator pins in order to minimize output distortion and start-up stabilization time. Refer to the crystal/ceramic resonator manufacturer for more details (frequency, package, accuracy...).

Table 22. 4/8 MHz crystal / ceramic resonator oscillator (XT1/XT2)<sup>(1)</sup>

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
fosc4M	Oscillator frequency	4 MHz Crystal/Resonator Oscillator connected on XT1/XT2 XTDIV=0 or 8 MHz Crystal/Resonator Oscillator connected on XT1/XT2 XTDIV=1		4		MHz
R <sub>F</sub>	Feedback resistor		200	240	270	kΩ
C <sub>L1</sub> <sup>(2)</sup> C <sub>L2</sub>	Recommended load capacitance versus equivalent serial resistance of the crystal or ceramic resonator (R <sub>S</sub> ) <sup>(3)</sup>	R <sub>S</sub> =200Ω			60	pF
i <sub>2</sub>	XT2 driving current	V <sub>DD_IO</sub> =3.3 V or 5.0 V		425		μΑ
t <sub>SU(OSC4M)</sub> <sup>(4)</sup>	Startup time at V <sub>DD_IO</sub> power-up			1		ms

- 1. Resonator characteristics given by the crystal/ceramic resonator manufacturer.
- 2. For C<sub>L1</sub> and C<sub>L2</sub> it is recommended to use high-quality ceramic capacitors in the 5-pF to 25-pF range (typ.) designed for high-frequency applications and selected to match the requirements of the crystal or resonator. C<sub>L1</sub> and C<sub>L2</sub>, are usually the same size. The crystal manufacturer typically specifies a load capacitance which is the series combination of C<sub>L1</sub> and C<sub>L2</sub>. PCB and MCU pin capacitance must be included when sizing C<sub>L1</sub> and C<sub>L2</sub> (10 pF can be used as a rough estimate of the combined pin and board capacitance).
- 3. The relatively low value of the RF resistor offers a good protection against issues resulting from use in a humid environment, due to the induced leakage and the bias condition change. However, it is recommended to take this point into account if the MCU is used in tough humidity conditions.
- 4. t<sub>SU(OSC4M)</sub> is the typical start-up time measured from the moment V<sub>DD\_IO</sub> is powered (with a quick V<sub>DD\_IO</sub> ramp-up from 0 to 3.3V (<50μs) to a stabilized 4MHz oscillation is reached. This value is measured for a standard crystal resonator and it can vary significantly with the crystal/ceramic resonator manufacturer.</p>

Figure 21. Typical application with a 4 or 8 MHz crystal or ceramic resonator



# OSC32K crystal / ceramic resonator oscillator

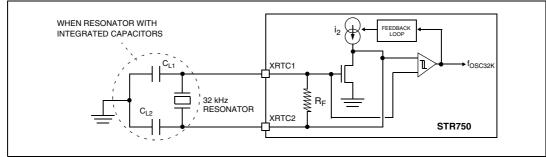
The STR7 RTC clock can be supplied with a 32.768 kHz Crystal/Ceramic resonator oscillator. All the information given in this paragraph are based on product characterisation with specified typical external components. In the application, the resonator and the load capacitors have to be placed as close as possible to the oscillator pins in order to minimize output distortion and start-up stabilization time. Refer to the crystal/ceramic resonator manufacturer for more details (frequency, package, accuracy...).

Table 23. OSC32K crystal / ceramic resonator oscillator

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f <sub>OSC32K</sub>	Oscillator Frequency			32.768		kHz
R <sub>F</sub>	Feedback resistor	V <sub>DD_IO</sub> =3.3 V or 5.0 V	270	310	370	kΩ
C <sub>L1</sub>	Recommended load capacitance versus equivalent serial resistance of the crystal or ceramic resonator (R <sub>S</sub> ) <sup>(1)</sup>	R <sub>S</sub> =40KΩ		12.5	15	pF
i <sub>2</sub>	XT2 driving current	V <sub>DD_IO</sub> =3.3 V or 5.0 V V <sub>IN</sub> =V <sub>SS</sub>	1		5	μА
t <sub>SU(OSC32K)</sub> (2)	Startup time	V <sub>DD_IO</sub> is stabilized		2.5		s

The oscillator selection can be optimized in terms of supply current using an high quality resonator with small R<sub>S</sub> value. Refer to crystal/ceramic resonator manufacturer for more details

Figure 22. Typical application with a 32.768 kHz crystal or ceramic resonator



### **PLL** characteristics

### **PLL Jitter Terminology**

Self-referred single period jitter (period jitter)

Period Jitter is defined as the difference of the maximum period  $(T_{max})$  and minimum period  $(T_{min})$  at the output of the PLL where  $T_{max}$  is the maximum time difference between 2 consecutive clock rising edges and  $T_{min}$  is the minimum time difference between 2 consecutive clock rising edges.

See Figure 23

Self-referred long term jitter (N period jitter)

Self-referred long term Jitter is defined as the difference of the maximum period  $(T_{max})$  and minimum period  $(T_{min})$  at the output of the PLL where  $T_{max}$  is the maximum time

t<sub>SU(OSC32K)</sub> is the start-up time measured from the moment it is enabled (by software) to a stabilized 32 kHz oscillation is reached. This value is measured for a standard crystal resonator and it can vary significantly with the crystal/ceramic resonator manufacturer

difference between N+1 consecutive clock rising edges and T<sub>min</sub> is the minimum time difference between N+1 consecutive clock rising edges.

N should be kept sufficiently large to have a long term jitter (ex: thousands).

For N=1, this becomes the single period jitter.

See Figure 23

Cycle-to-cycle jitter (N period jitter)

This corresponds to the time variation between adjacent cycles over a random sample of adjacent clock cycles pairs. Jitter(cycle-to-cycle) = Max(Tcycle n- Tcycle n-1) for n=1 to N.

See Figure 24

Figure 23. Self-referred jitter (single and long term)

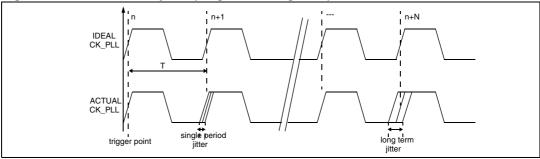
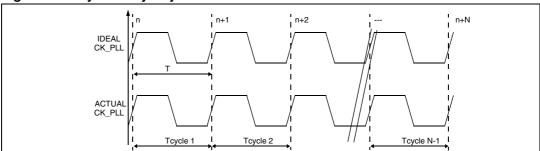


Figure 24. Cycle-to-cycle jitter



### **PLL** characteristics

Subject to general operating conditions for  $V_{DD\_IO}$ , and  $T_A$ .

Table 24. PLL characteristics

Symbol	Parameter	Test Conditions		Unit		
Symbol	raiailletei	rest Conditions	Min	Тур	Max <sup>(1)</sup>	Offic
f	PLL input clock			4.0		MHz
f <sub>PLL_IN</sub>	PLL input clock duty cycle		40		60	%
f <sub>PLL_OUT</sub>	PLL multiplier output clock	f <sub>PLL_IN</sub> x 24			165	MHz
f <sub>VCO</sub>	VCO frequency range	When PLL operates (locked)	336		960	MHz
t <sub>LOCK</sub>	PLL lock time				300	μS
∆t <sub>JITTER1</sub> (2)(3)	Single period jitter (+/-3 $\Sigma$ peak to peak)	$f_{PLL\_IN} = 4 \text{ MHz}^{(4)}$ $V_{DD\_IO}$ is stable			+/-250	ps
∆t <sub>JITTER2</sub> (2)(3)	Long term jitter (+/-3 $\Sigma$ peak to peak)	f <sub>PLL_IN</sub> = 4 MHz <sup>(4)</sup> V <sub>DD_IO</sub> is stable			+/-2.5	ns
∆t <sub>JITTER3</sub> (2)(3)	Cycle to cycle jitter (+/-3 $\Sigma$ peak to peak)	$f_{PLL\_IN} = 4 \text{ MHz}^{(4)}$ $V_{DD\_IO}$ is stable			+/-500	ps

<sup>1.</sup> Data based on product characterisation, not tested in production.

# Internal RC oscillators (FREEOSC & LPOSC)

Subject to general operating conditions for  $V_{DD\ IO}$ , and  $T_A$ .

Table 25. Internal RC oscillators (FREEOSC & LPOSC)

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f <sub>CK_FREEOSC</sub>	FREEOSC Oscillator Frequency		3	5	8	MHz
f <sub>CK_LPOSC</sub>	LPOSC Oscillator Frequency		150	300	500	kHz

<sup>2.</sup> Refer to jitter terminology in : PLL characteristics on page 47 for details on how jitter is specified.

<sup>3.</sup> The jitter specification holds true only up to 50mV (peak-to-peak) noise on  $V_{DDA\_PLL}$  and  $V_{18}$  supplies. Jitter will increase if the noise is more than 50mV. In addition, it assumes that the input clock has no jitter.

The PLL parameters (MX1, MX0, PRESC1, PRESC2) must respect the constraints described in: PLL characteristics on page 47.

# 6.3.6 Memory characteristics

# Flash memory

Subject to general operating conditions for  $V_{DD\_IO}$  and  $V_{18}$ ,  $T_A$  = -40 to 105 °C unless otherwise specified.

Table 26. Flash memory characteristics

Cumbal	Dava-mata-r	Took Conditions	Value		l lmit
Symbol	Parameter	Test Conditions	Тур	Max <sup>(1)</sup>	Unit
t <sub>PW</sub>	Word Program		35		μS
t <sub>PDW</sub>	Double Word Program		60		μS
t <sub>PB0</sub>	Bank 0 Program (256K)	Single Word programming of a checker-board pattern	2	4.9 <sup>(2)</sup>	s
t <sub>PB1</sub>	Bank 1 Program (16K)	Single Word programming of a checker-board pattern	125	224 <sup>(2)</sup>	ms
t <sub>ES</sub>	Sector Erase (64K)	Not preprogrammed (all 1) Preprogrammed (all 0)	1.54 1.176	2.94 <sup>(2)</sup> 2.38 <sup>(2)</sup>	S
t <sub>ES</sub>	Sector Erase (8K)	Not preprogrammed (all 1) Preprogrammed (all 0)	392 343	560 <sup>(2)</sup> 532 <sup>(2)</sup>	ms
t <sub>ES</sub>	Bank 0 Erase (256K)	Not preprogrammed (all 1) Preprogrammed (all 0)	8.0 6.6	13.7 11.2	s
t <sub>ES</sub>	Bank 1 Erase (16K)	Not preprogrammed (all 1) Preprogrammed (all 0)	0.9 0.8	1.5 1.3	S
t <sub>RPD</sub>	Recovery when disabled			20	μS
t <sub>PSL</sub>	Program Suspend Latency			10	μS
t <sub>ESL</sub>	Erase Suspend Latency			300	μS

<sup>1.</sup> Data based on characterisation not tested in production

Table 27. Flash memory endurance and data retention

Symbol	Parameter	Conditions		Value	Unit	
	Farameter	Conditions	Min <sup>(1)</sup> Typ			
N <sub>END_B0</sub>	Endurance (Bank 0 sectors)		10			kcycles
N <sub>END_B1</sub>	Endurance (Bank 1 sectors)		100			kcycles
Y <sub>RET</sub>	Data Retention	T <sub>A</sub> =85° C	20			Years
t <sub>ESR</sub>	Erase Suspend Rate	Min time from Erase Resume to next Erase Suspend	20			ms

<sup>1.</sup> Data based on characterisation not tested in production.

<sup>2. 10</sup>K program/erase cycles.

#### 6.3.7 EMC characteristics

Susceptibility tests are performed on a sample basis during product characterization.

# Functional EMS (electro magnetic susceptibility)

Based on a simple running application on the product (toggling 2 LEDs through I/O ports), the product is stressed by two electro magnetic events until a failure occurs (indicated by the LEDs).

- ESD: Electro-Static Discharge (positive and negative) is applied on all pins of the device until a functional disturbance occurs. This test conforms with the IEC 1000-4-2 standard.
- FTB: A Burst of Fast Transient voltage (positive and negative) is applied to V<sub>DD</sub> and V<sub>SS</sub> through a 100pF capacitor, until a functional disturbance occurs. This test conforms with the IEC 1000-4-4 standard.

A device reset allows normal operations to be resumed. The test results are given in the table below based on the EMS levels and classes defined in application note AN1709.

### Designing hardened software to avoid noise problems

EMC characterization and optimization are performed at component level with a typical application environment and simplified MCU software. It should be noted that good EMC performance is highly dependent on the user application and the software in particular.

Therefore it is recommended that the user applies EMC software optimization and prequalification tests in relation with the EMC level requested for his application.

#### Software recommendations:

The software flowchart must include the management of runaway conditions such as:

- Corrupted program counter
- Unexpected reset
- Critical Data corruption (control registers...)

### **Prequalification trials:**

Most of the common failures (unexpected reset and program counter corruption) can be reproduced by manually forcing a low state on the RESET pin or the Oscillator pins for 1 second

To complete these trials, ESD stress can be applied directly on the device, over the range of specification values. When unexpected behaviour is detected, the software can be hardened to prevent unrecoverable errors occurring (see application note AN1015).

Table 28. EMC characteristics

Symbol	Parameter	Conditions	Level/ Class
V <sub>FESD</sub>	Voltage limits to be applied on any I/O pin to induce a functional disturbance	$V_{DD\_IO}$ =3.3 V or 5 V, $T_A$ =+25° C, $f_{CK\_SYS}$ =32 MHz conforms to IEC 1000-4-2	Class A
V <sub>EFTB</sub>	Fast transient voltage burst limits to be applied through 100pF on $V_{DD}$ and $V_{SS}$ pins to induce a functional disturbance	$V_{DD\_IO}$ =3.3 V or 5 V, $T_A$ =+25° C, $f_{CK\_SYS}$ =32 MHz conforms to IEC 1000-4-4	Class A

# Electro magnetic interference (EMI)

Based on a simple application running on the product (toggling 2 LEDs through the I/O ports), the product is monitored in terms of emission. This emission test is in line with the norm SAE J 1752/3 which specifies the board and the loading of each pin.

Table 29. EMI characteristics

Symbo I	Parameter	Conditions	Monitored	Max vs. [f <sub>OSC4M</sub> /f <sub>HCLK</sub> ]		Unit
	Parameter	Conditions	Frequency Band	4/32MHz	4/60MHz	Offic
		Flash devices:	0.1 MHz to 30 MHz	22	26	
		V <sub>DD_IO</sub> =3.3 V or 5 V, T <sub>A</sub> =+25° C,	30 MHz to 130 MHz	31	26	dBμV
S <sub>EMI</sub>	Peak level	LQFP64 package	130 MHz to 1 GHz	Hz 19	23	
		conforming to SAE J 1752/3	SAE EMI Level	>4	>4	-

## Absolute maximum ratings (electrical sensitivity)

Based on three different tests (ESD, LU and DLU) using specific measurement methods, the product is stressed in order to determine its performance in terms of electrical sensitivity. For more details, refer to the application note AN1181.

## Electro-Static discharge (ESD)

Electro-Static Discharges (a positive then a negative pulse separated by 1 second) are applied to the pins of each sample according to each pin combination. The sample size depends on the number of supply pins in the device (3 parts\*(n+1) supply pin). Two models can be simulated: Human Body Model and Machine Model. This test conforms to the JESD22-A114A/A115A standard.

Table 30. Absolute maximum ratings

Symbol	Ratings	Conditions	Maximum value <sup>(1)</sup>	Unit
V <sub>ESD(HBM)</sub>	Electro-static discharge voltage (Human Body Model)		2000	
V <sub>ESD(MM)</sub>	Electro-static discharge voltage (Machine Model)	T <sub>A</sub> =+25° C	200	V
V <sub>ESD(CDM)</sub>	Electro-static discharge voltage (Charge Device Model)		750	

<sup>1.</sup> Data based on product characterisation, not tested in production.

# Static and dynamic latch-up

- LU: 3 complementary static tests are required on 10 parts to assess the latch-up performance. A supply overvoltage (applied to each power supply pin) and a current injection (applied to each input, output and configurable I/O pin) are performed on each sample. This test conforms to the EIA/JESD 78 IC latch-up standard. For more details, refer to the application note AN1181.
- DLU: Electro-Static Discharges (one positive then one negative test) are applied to
  each pin of 3 samples when the micro is running to assess the latch-up performance in
  dynamic mode. Power supplies are set to the typical values, the oscillator is connected
  as near as possible to the pins of the micro and the component is put in reset mode.
  This test conforms to the IEC1000-4-2 and SAEJ1752/3 standards. For more details,
  refer to the application note AN1181.

Table 31. Electrical sensitivities

Symbol	Parameter	Conditions	Class <sup>(1)</sup>
LU	Static latch-up class	T <sub>A</sub> =+25° C T <sub>A</sub> =+85° C T <sub>A</sub> =+105° C	Class A
DLU	Dynamic latch-up class	$V_{DD}$ = 5.5 V, $f_{OSC4M}$ =4 MHz, $f_{CK\_SYS}$ =32 MHz, $T_A$ =+25° C	Class A

Class description: A Class is an STMicroelectronics internal specification. All its limits are higher than the JEDEC specifications, that means when a device belongs to Class A it exceeds the JEDEC standard. B Class strictly covers all the JEDEC criteria (international standard).

# 6.3.8 I/O port pin characteristics

### **General characteristics**

Subject to general operating conditions for  $V_{DD\_IO}$  and  $T_A$  unless otherwise specified.

Table 32. General characteristics

	I/O stati	ic characteris	stics				
Symbol	Parameter	Con	ditions	Min	Тур	Max	Unit
V <sub>IL</sub>	Input low level voltage					0.8	V
V <sub>IH</sub>	Input high level voltage	TTL ports		2			V
V <sub>hys</sub>	Schmitt trigger voltage hysteresis <sup>(1)</sup>	TTE porte			400		mV
I <sub>INJ(PIN)</sub>	Injected Current on any I/O pin					± 4	
ΣΙ <sub>ΙΝ</sub> Ι(ΡΙΝ	Total injected current (sum of all I/O and control pins)				± 25	mA	
I <sub>lkg</sub>	Input leakage current on robust pins	See Section	72				
	Input leakage current <sup>(3)</sup>	V <sub>SS</sub> ≤V <sub>IN</sub> ≤V <sub>DE</sub>	0_10			±1	^
I <sub>S</sub>	Static current consumption <sup>(4)</sup>	Floating inpu	t mode		200		μΑ
В	Weak pull-up equivalent	V V	V <sub>DD_IO</sub> =3.3 V	50	95	200	kΩ
R <sub>PU</sub>	resistor <sup>(5)</sup>	V <sub>IN</sub> =V <sub>SS</sub>	V <sub>DD_IO</sub> =5 V	20	58	150	kΩ
В	Weak pull-down equivalent	V V	V <sub>DD_IO</sub> =3.3 V	25	80	180	kΩ
$R_{PD}$	resistor <sup>(5)</sup>	V <sub>IN</sub> =V <sub>DD_IO</sub>	V <sub>DD_IO</sub> =5 V	20	50	120	kΩ
C <sub>IO</sub>	I/O pin capacitance		•		5		pF
t <sub>w(IT)in</sub>	External interrupt/wake-up lines pulse time <sup>(6)</sup>			2			T <sub>AP</sub>

<sup>1.</sup> Hysteresis voltage between Schmitt trigger switching levels.

When the current limitation is not possible, the V<sub>IN</sub> absolute maximum rating must be respected, otherwise
refer to I<sub>INJ(PIN)</sub> specification. A positive injection is induced by V<sub>IN</sub>>V<sub>DD\_IO</sub> while a negative injection is
induced by V<sub>IN</sub><V<sub>SS</sub>. Refer to Section 6.2 on page 32 for more details.

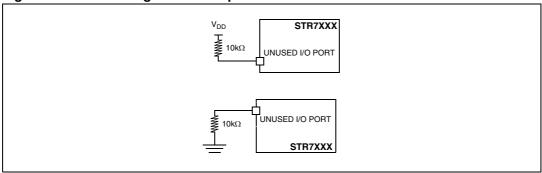
<sup>3.</sup> Leakage could be higher than max. if negative current is injected on adjacent pins.

<sup>4.</sup> Configuration not recommended, all unused pins must be kept at a fixed voltage: using the output mode of the I/O for example or an external pull-up or pull-down resistor (see *Figure 25*). Data based on design simulation and/or technology characteristics, not tested in production.

<sup>5.</sup> The  $R_{PU}$  pull-up and  $R_{PD}$  pull-down equivalent resistor are based on a resistive transistor.

To generate an external interrupt, a minimum pulse width has to be applied on an I/O port pin configured as an external interrupt source.

Figure 25. Connecting unused I/O pins



## **Output driving current**

The GP I/Os have different drive capabilities:

- O2 outputs can sink or source up to +/-2 mA.
- O4 outputs can sink or source up to +/-4 mA.
- outputs can sink or source up to  $\pm$ -8 mA or can sink  $\pm$ 20 mA (with a relaxed  $V_{OL}$ ).

In the application, the user must limit the number of I/O pins which can drive current to respect the absolute maximum rating specified in *Section 6.2.2*:

- The sum of the current sourced by all the I/Os on V<sub>DD\_IO,</sub> plus the maximum RUN consumption of the MCU sourced on V<sub>DD\_IO,</sub> can not exceed the absolute maximum rating IV<sub>DD\_IO</sub>.
- The sum of the current sunk by all the I/Os on V<sub>SS\_IO</sub> plus the maximum RUN consumption of the MCU sunk on V<sub>SS\_IO</sub> can not exceed the absolute maximum rating IV<sub>SS\_IO</sub>.

Subject to general operating conditions for  $V_{DD\ IO}$  and  $T_A$  unless otherwise specified.

Table 33. Output driving current

I/O Output drive characteristics for  $V_{DD\_IO}$  = 3.0 to 3.6 V and EN33 bit =1 or  $V_{DD\_IO}$  = 4.5 to 5.5 V and EN33 bit =0

	of the price and the state of t								
I/O Type	Symbol	Parameter	Conditions	Min	Max	Unit			
O2	V <sub>OL</sub> <sup>(1)</sup>	Output low level voltage for a standard I/O pin when 8 pins are sunk at same time	I <sub>IO</sub> =+2 mA		0.4				
	V <sub>OH</sub> <sup>(2)</sup>	Output high level voltage for an I/O pin when 4 pins are sourced at same time	I <sub>IO</sub> =-2 mA	V <sub>DD_IO</sub> -0.8					
04	V <sub>OL</sub> <sup>(1)</sup>	Output low level voltage for a standard I/O pin when 8 pins are sunk at same time	I <sub>IO</sub> =+4 mA		0.4				
	V <sub>OH</sub> <sup>(2)</sup>	Output high level voltage for an I/O pin when 4 pins are sourced at same time	I <sub>IO</sub> =-4 mA	V <sub>DD_IO</sub> -0.8		V			
	V <sub>OL</sub> <sup>(1)</sup>	Output low level voltage for a standard I/O pin when 8 pins are sunk at same time	I <sub>IO</sub> =+8 mA		0.4				
O8		Output low level voltage for a high sink I/O pin when 4 pins are sunk at same time	$I_{IO}$ =+20 mA, $T_A$ ≤85°C $T_A$ ≥85°C		1.3 1.5				
			I <sub>IO</sub> =+8 mA		0.4				
	V <sub>OH</sub> <sup>(2)</sup>	Output high level voltage for an I/O pin when 4 pins are sourced at same time	I <sub>IO</sub> =-8 mA	V <sub>DD_IO</sub> -0.8					

<sup>1.</sup> The  $I_{|O}$  current sunk must always respect the absolute maximum rating specified in Section 6.2.2 and the sum of  $I_{|O}$  (I/O ports and control pins) must not exceed  $I_{VSS\_IO}$ .

<sup>2.</sup> The  $I_{IO}$  current sourced must always respect the absolute maximum rating specified in Section 6.2.2 and the sum of  $I_{IO}$  (I/O ports and control pins) must not exceed  $I_{VDD\_IO}$ .

# **Output speed**

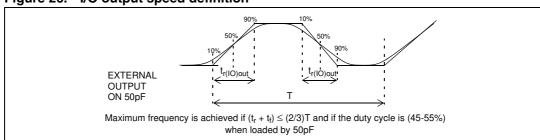
Subject to general operating conditions for  $V_{DD\_IO}$  and  $T_A$  unless otherwise specified.

Table 34. Output speed

	I/O dynamic characteristics for V <sub>DD_IO</sub> = 3.0 to 3.6V and EN33 bit =1 or V <sub>DD_IO</sub> = 4.5 to 5.5V and EN33 bit =0									
I/O Type	Symbol	Parameter	Conditions	Min	Тур	Max	Unit			
	f <sub>max(IO)out</sub>	Maximum Frequency <sup>(1)</sup>	C <sub>L</sub> =50 pF			10	MHz			
O2	t <sub>f(IO)out</sub>	Output high to low level fall time <sup>(2)</sup>	C <sub>L</sub> =50 pF			30	ns			
	t <sub>r(IO)out</sub>	Output low to high level rise time <sup>(2)</sup>	Between 10% and 90%			33	115			
	f <sub>max(IO)out</sub>	Maximum Frequency <sup>(1)</sup>	C <sub>L</sub> =50 pF			25	MHz			
O4	t <sub>f(IO)out</sub>	Output high to low level fall time <sup>(2)</sup>	C <sub>L</sub> =50 pF			12	nc			
	t <sub>r(IO)out</sub>	Output low to high level rise time <sup>(2)</sup>	Between 10% and 90%			14	ns			
	f <sub>max(IO)out</sub>	Maximum Frequency <sup>(1)</sup>	C <sub>L</sub> =50pF			40	MHz			
O8	t <sub>f(IO)out</sub>	Output high to low level fall time <sup>(2)</sup>	C <sub>L</sub> =50 pF			6	ne			
	t <sub>r(IO)out</sub>	Output low to high level rise time <sup>(2)</sup>	Between 10% and 90%			6	ns			

- 1. The maximum frequency is defined as described in Figure 26.
- 2. Data based on product characterisation, not tested in production.

Figure 26. I/O output speed definition



# **NRSTIN and NRSTOUT pins**

NRSTIN Pin Input Driver is TTL/LVTTL as for all GP I/Os. A permanent pull-up is present which is the same as RPIJ (see : General characteristics on page 54)

NRSTOUT Pin Output Driver is equivalent to the O2 type driver except that it works only as an open-drain (the P-MOS is de-activated). A permanent pull-up is present which is the same as R<sub>PU</sub> (see : General characteristics on page 54)

Subject to general operating conditions for V<sub>DD IO</sub> and T<sub>A</sub> unless otherwise specified.

Table 35. NRSTIN and NRSTOUT pins

Symbol	Parameter	Coi	nditions	Min	Typ 1)	Max	Unit
V <sub>IL(NRSTIN)</sub>	NRSTIN Input low level voltage <sup>(1)</sup>					0.8	V
V <sub>IH(NRSTIN)</sub>	NRSTIN Input high level voltage <sup>(1)</sup>			2			V
V <sub>hys(NRSTIN)</sub>	NRSTIN Schmitt trigger voltage hysteresis <sup>(2)</sup>				400		mV
V <sub>OL(NRSTIN)</sub>	NRSTOUT Output low level voltage <sup>(3)</sup>	I <sub>IO</sub> =+2 mA				0.4	V
B	NRSTIN Weak pull-up equivalent resistor <sup>(4)</sup>	V <sub>IN</sub> =V <sub>SS</sub>	V <sub>DD_IO</sub> =3.3 V	25	50	100	kΩ
R <sub>PU(NRSTIN)</sub>		V <sub>DD_IO</sub> =5 V	V <sub>DD_IO</sub> =5 V	20	31	100	kΩ
t <sub>w(RSTL)out</sub>	Generated reset pulse duration (visible at NRSTOUT pin) <sup>(5)</sup>	Internal re	set source	15	20		μS
	External reset pulse hold time	At V <sub>DD_IO</sub>	power-up <sup>(5)</sup>	20			μS
t <sub>h(RSTL)in</sub>	at NRSTIN pin <sup>(6)</sup>	When V <sub>DI</sub> establishe	)_ O is d <sup>(5)</sup>	1			μS
t <sub>g(RSTL)in</sub>	maximum negative spike duration filtered at NRSTIN pin <sup>(7)</sup>	spikes mu	petween two st be higher f the spike		150		ns

- 1. Data based on product characterisation, not tested in production.
- 2. Hysteresis voltage between Schmitt trigger switching levels.
- 3. The  $I_{\rm IO}$  current sunk must always respect the absolute maximum rating specified in Section 6.2.2 and the sum of  $I_{\rm IO}$  (I/O ports and control pins) must not exceed  $I_{\rm VSS}$ .
- The R<sub>PU</sub> pull-up equivalent resistor are based on a resistive transistor
- To guarantee the reset of the device, a minimum pulse of 15 µs has to be applied to the internal reset. At  $V_{DD}$   $_{IO}$  power-up, the built-in reset stretcher may not generate the 15  $\mu s$  pulse duration while once  $V_{DD}$   $_{IO}$  is established, an external reset pulse will be internally stretched up to 15  $\mu s$  thanks to the reset pulse stretcher.
- 6. The reset network (the resistor and two capacitors) protects the device against parasitic resets, especially in noisy environments.
- In fact the filter is made to ignore all incoming pulses with short duration:
   all negative spikes with a duration less than 150 ns are filtered

  - all trains of negative spikes with a ratio of 1/2 are filtered. This means that all spikes with a maximum duration of 150 ns with minimum interval between spikes of 75 ns are filtered. Data guaranteed by design, not tested in production.

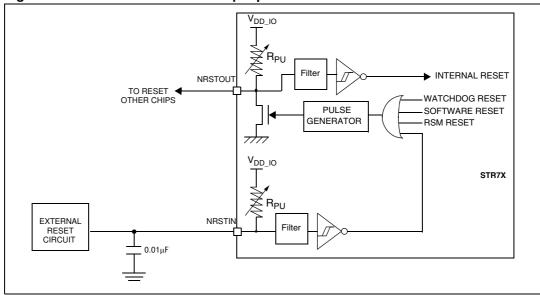


Figure 27. Recommended NRSTIN pin protection

 The user must ensure that the level on the NRSTIN pin can go below the V<sub>IL(NRSTIN)</sub> max. level specified in NRSTIN and NRSTOUT pins on page 58. Otherwise the reset will not be taken into account internally.

# 6.3.9 TB and TIM timer characteristics

Subject to general operating conditions for  $V_{DD\_IO}$ ,  $f_{CK\_SYS}$ , and  $T_A$  unless otherwise specified.

Refer to *Section 6.3.8: I/O port pin characteristics on page 54* for more details on the input/output alternate function characteristics (output compare, input capture, external clock, PWM output...).

Table 36. TB and TIM timers

Symbol	Parameter		Conditions	Min	Тур	Max	Unit				
T	Input capture pulse time	TIM0,1,2		2			t <sub>CK_TIM</sub>				
			$f_{CK\_TIM(MAX)} = f_{CK\_SYS}$	1			t <sub>CK_TIM</sub>				
t	Timer resolution	TB	f <sub>CK_TIM</sub> = f <sub>CK_SYS</sub> = 60 MHz	16.6 <sup>(1)</sup>			ns				
t <sub>res(TIM)</sub>	time <sup>(1)</sup>		$f_{CK\_TIM(MAX)} = f_{CK\_SYS}$	1			t <sub>CK_TIM</sub>				
				TIM0,1,2	f <sub>CK_TIM</sub> = f <sub>CK_SYS</sub> = 60MHz	16.6 <sup>(1)</sup>			ns		
t	Timer		$f_{CK\_TIM(MAX)} = f_{CK\_SYS}$	0		f <sub>CK_TIM</sub> /4	MHz				
	frequency on TI1 or TI2		TIM0,1,2	f <sub>CK_TIM</sub> = f <sub>CK_SYS</sub> = 60 MHz	0		15	MHz			
Res <sub>TIM</sub>	Timer resolution					16	bit				
	16-bit	16-bit	16-bit	16-bit			1		65536	t <sub>CK_TIM</sub>	
t	Counter clock period when internal clock	TB	f <sub>CK_TIM</sub> = f <sub>CK_SYS</sub> = 60 MHz	0.0166		1092	μs				
<sup>t</sup> COUNTER	is selected			1		65536	t <sub>CK_TIM</sub>				
	(16-bit Prescaler)	TIM0,1,2	f <sub>CK_TIM</sub> = f <sub>CK_SYS</sub> = 60 MHz	0.0166		1092	μs				
						65536x65536	t <sub>CK_TIM</sub>				
t	Maximum Possible	TB	f <sub>CK_TIM</sub> = f <sub>CK_SYS</sub> = 60 MHz			71.58	S				
t <sub>MAX_COUNT</sub>	Count					65536x65536	t <sub>CK_TIM</sub>				
						TIM0,1,2	f <sub>CK_TIM</sub> = f <sub>CK_SYS</sub> = 60 MHz			71.58	S

Take into account the frequency limitation due to the I/O speed capability when outputting the PWM to I/O pin, described in : Output speed on page 57.

Table 37. PWM Timer (PWM)

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		$f_{CK\_TIM(MAX)} = f_{CK\_SYS}$	1			t <sub>CK_TIM</sub>
t <sub>res(PWM)</sub>	PWM resolution time	f <sub>CK_TIM</sub> = f <sub>CK_SYS</sub> = 60 MHz	16.6 <sup>(1)</sup>			ns
Res <sub>PWM</sub>	PWM resolution				16	bit
V <sub>OS</sub> <sup>(1)</sup>	PWM/DAC output step voltage	V <sub>DD_IO</sub> =3.3 V, Res=16-bits		50 <sup>(1)</sup>		μV
VOS` /		V <sub>DD_IO</sub> =5.0 V, Res=16-bits		76 <sup>(1)</sup>		μV
	Timer clock period when internal clock is selected		1		65536	t <sub>CK_TIM</sub>
<sup>t</sup> COUNTER		f <sub>CK_TIM</sub> =60 MHz	0.0166		1087	μs
t	Maximum Possible				65536x 65536	t <sub>CK_TIM</sub>
t <sub>MAX_COUNT</sub>	Count	f <sub>CK_TIM</sub> = f <sub>CK_SYS</sub> = 60 MHz			71.58	S

<sup>1.</sup> Take into account the frequency limitation due to the I/O speed capability when outputting the PWM to an I/O pin, as described in : Output speed on page 57.

# 6.3.10 Communication interface characteristics

# SSP synchronous serial peripheral in master mode (SPI or TI mode)

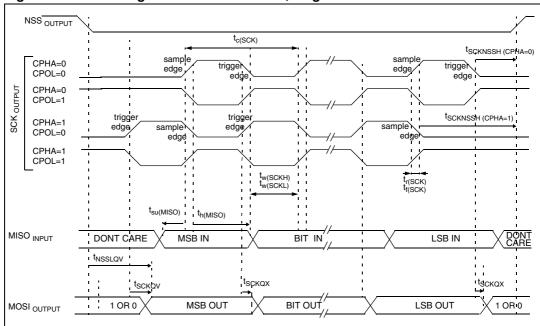
General operating conditions: V33, 3.0V to 3.3V, V18 =1.8V,  $C_L \approx 45$  pF.

Table 38. SSP master mode characteristics<sup>(1)</sup>

Symbol	Parameter	Condi	tions	Min	Max	Unit
f	SPI clock frequency <sup>(2)</sup>		SSP0		16	MHz
f <sub>SCK</sub>	SPI clock frequency.		SSP1		8	IVITZ
	SPI clock rise time		SSP0		14	
t <sub>r(SCK)</sub>	SPI Clock rise time		SSP1		33	
	SPI clock fall time		SSP0		11	
t <sub>f(SCK)</sub>	SPI Clock Idii time		SSP1		30	
t <sub>w(SCKH)</sub>	CCV high and law time		SSP0		19	
t <sub>w(SCKL)</sub>	SCK high and low time		SSP1		30	
+	NSS low to Data Output		SSP0		0.5t <sub>SCK</sub> +15ns	
t <sub>NSSLQV</sub>	MOSI valid time		SSP1		0.5t <sub>SCK</sub> +30ns	
	SCK last edge to NSS high	CPHA = 0	SSP0		0.5t <sub>SCK</sub> +15ns	
		CPHA = 0	SSP1		0.5t <sub>SCK</sub> +30ns	
t <sub>SCKNSSH</sub>		CPHA = 1	SSP0		t <sub>SCK</sub> +15ns	ns
			SSP1		t <sub>SCK</sub> +30ns	
	SCK trigger edge to data		SSP0		15	
t <sub>SCKQV</sub>	output MOSI valid time		SSP1		30	
+	SCK trigger edge to data		SSP0	0		
t <sub>SCKQX</sub>	output MOSI invalid time		SSP1	0		
	Data input (MISO) setup		SSP0	25		
t <sub>su</sub>	time w.r.t SCK sampling edge		SSP1	25		
t.	Data input (MISO) hold time		SSP0	0		
t <sub>h</sub>	w.r.t SCK sampling edge		SSP1	0		

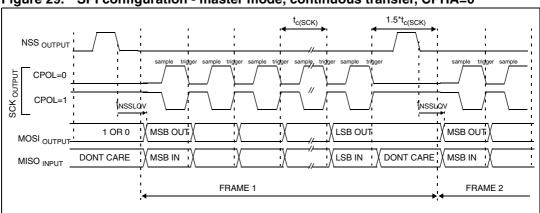
<sup>1.</sup> Data based on characterisation results, not tested in production.

<sup>2.</sup> Max frequency for the 2 SSPs is  $f_{PCLK}/2$ ;  $f_{PCLK}$  max = 32 MHz. This takes into account the frequency limitation due to I/O speed capability. SSP0 uses IO4 type while SSP1 uses IO2 type I/Os.



SPI configuration - master mode, single transfer Figure 28.





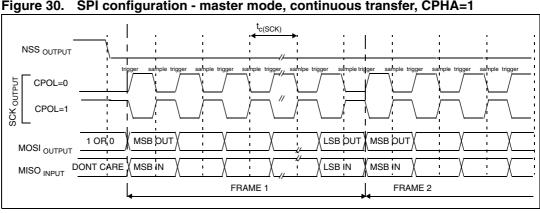


Figure 30. SPI configuration - master mode, continuous transfer, CPHA=1

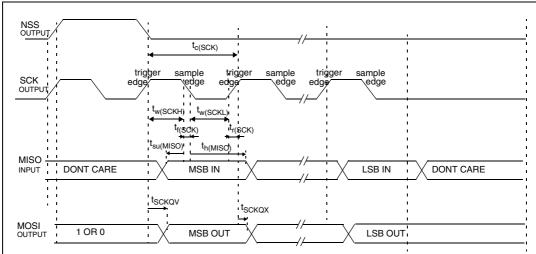
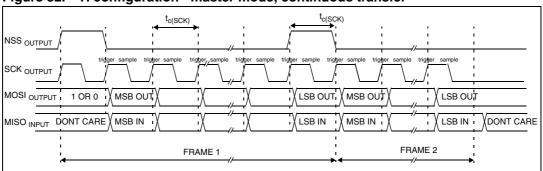


Figure 31. TI configuration - master mode, single transfer





# SSP synchronous serial peripheral in slave mode (SPI or TI mode)

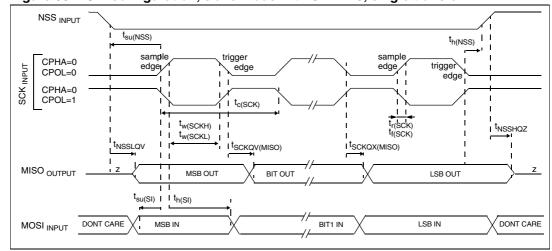
Subject to general operating conditions with  $C_L \approx 45 \ pF$ 

Table 39. SSP slave mode characteristics<sup>(1)</sup>

Symbol	Parameter	Cor	nditions	Min	Max	Unit
f	CDI alask francisco		SSP0		2.66 MHz	MHz
f <sub>SCK</sub>	SPI clock frequency		SSP1		(f <sub>PLCK</sub> /12)	
	NSS input setup time w.r.t		SSP0	0		
t <sub>su(NSS)</sub>	SCK first edge		SSP1	0		
	NSS input hold time w.r.t		SSP0	t <sub>PCLK</sub> +15ns		
t <sub>h(NSS)</sub>	SCK last edge		SSP1	t <sub>PCLK</sub> +15ns		
	NSS low to Data Output MISO valid time		SSP0	2t <sub>PCLK</sub>	3t <sub>PCLK</sub> +30 ns	
t <sub>NSSLQV</sub>			SSP1	2t <sub>PCLK</sub>	3t <sub>PCLK</sub> +30 ns	
+	NSS low to Data Output MISO invalid time		SSP0	2t <sub>PCLK</sub>	3t <sub>PCLK</sub> +15 ns	
t <sub>NSSLQZ</sub>			SSP1	2t <sub>PCLK</sub>	3t <sub>PCLK</sub> +15 ns	no
	SCK trigger edge to data output MISO valid time		SSP0		15	ns
tsckqv			SSP1		30	
	SCK trigger edge to data		SSP0	2t <sub>PCLK</sub>		
tsckqx	output MISO invalid time		SSP1	2t <sub>PCLK</sub>		
+	MOSI setup time w.r.t SCK		SSP0	0		
t <sub>su(MOSI)</sub>	sampling edge		SSP1	0		
+	MOSI hold time w.r.t SCK		SSP0	3t <sub>PCLK</sub> +15 ns		
t <sub>h(MOSI)</sub>	sampling edge		SSP1	3t <sub>PCLK</sub> +15 ns		

<sup>1.</sup> Data based on characterisation results, not tested in production.

Figure 33. SPI configuration, slave mode with CPHA=0, single transfer



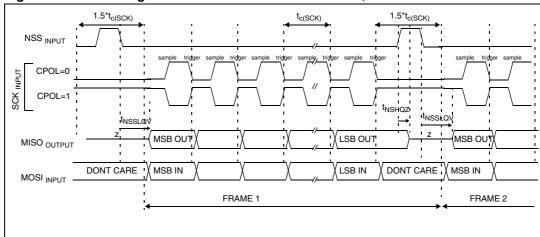
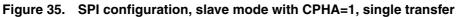


Figure 34. SPI configuration - slave mode with CPHA=0, continuous transfer



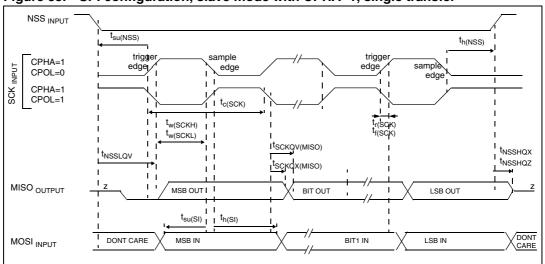
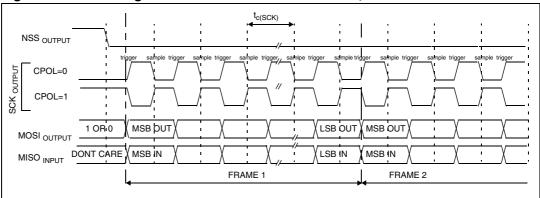


Figure 36. SPI configuration - slave mode with CPHA=1, continuous transfer



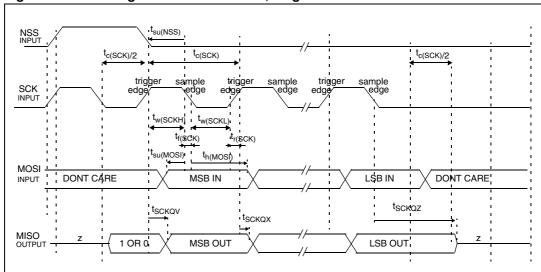
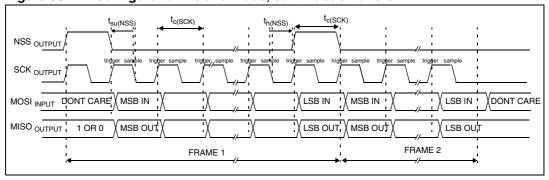


Figure 37. TI configuration - slave mode, single transfer





# SMI - serial memory interface

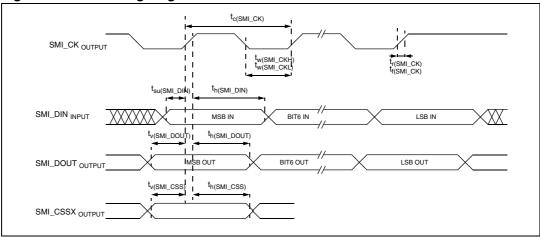
Subject to general operating conditions with  $C_1 \approx 30$  pF.

Table 40. SMI characteristics<sup>(1)</sup>

Symbol	Parameter	Min	Max	Unit
f	SMI clock frequency		32 <sup>(2)(3)</sup>	MUS
f <sub>SMI_CK</sub>			48 <sup>(4)</sup>	MHz
t <sub>r(SMI_CK)</sub>	SMI clock rise time		10	ns
t <sub>f(SMI_CK)</sub>	SMI clock fall time		8	115
t <sub>v(SMI_DOUT)</sub>	Data output valid time		10	
t <sub>h(SMI_DOUT)</sub>	Data output hold time		0	
t <sub>v(SMI_CSSx)</sub>	CSS output valid time		10	
t <sub>h(SMI_CSSx)</sub>	CSS output hold time		0	
t <sub>su(SMI_DIN)</sub>	Data input setup time	0		
t <sub>h(SMI_DIN)</sub>	Data input hold time	5		

- 1. Data based on characterisation results, not tested in production.
- 2. Max. frequency =  $f_{PCLK}/2 = 64/2 = 32 \text{ MHz}$ .
- 3. Valid for all temperature ranges: -40 to 105  $^{\circ}$ C, with 30 pF load capacitance.
- 4. Valid up to 60 °C, with 10 pF load capacitance.

Figure 39. SMI timing diagram



# I<sup>2</sup>C - Inter IC control interface

Subject to general operating conditions for  $V_{DD\_IO}$ ,  $f_{PCLK}$ , and  $T_A$  unless otherwise specified.

The I<sup>2</sup>C interface meets the requirements of the Standard I<sup>2</sup>C communication protocol described in the following table with the restriction mentioned below:

**Restriction:** The I/O pins which SDA and SCL are mapped to are not "True" Open-Drain: when configured as open-drain, the PMOS connected between the I/O pin and  $V_{DD\_IO}$  is disabled, but it is still present. Also, there is a protection diode between the I/O pin and  $V_{DD\_IO}$ . Consequently, when using this I<sup>2</sup>C in a multi-master network, it is

not possible to power off the STR7x while some another I<sup>2</sup>C master node remains powered on: otherwise, the STR7x will be powered by the protection diode.

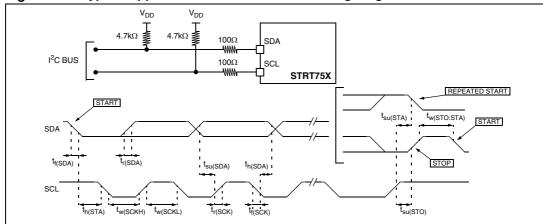
Refer to I/O port characteristics for more details on the input/output alternate function characteristics (SDA and SCL).

Table 41. SDA and SCL characteristics

Symbol	Parameter	Standard mode I <sup>2</sup> C		Fast mode I <sup>2</sup> C <sup>(1)</sup>		Unit
		Min <sup>(2)</sup>	Max <sup>(2)</sup>	Min <sup>(2)</sup>	Max <sup>(2)</sup>	
t <sub>w(SCLL)</sub>	SCL clock low time	4.7		1.3		6
t <sub>w(SCLH)</sub>	SCL clock high time	4.0		0.6		μS
t <sub>su(SDA)</sub>	SDA setup time	250		100		
t <sub>h(SDA)</sub>	SDA data hold time	0(3)		0 <sup>(4)</sup>	900 <sup>(3)</sup>	
t <sub>r(SDA)</sub> t <sub>r(SCL)</sub>	SDA and SCL rise time		1000	20+0.1C <sub>b</sub>	300	ns
t <sub>f(SDA)</sub> t <sub>f(SCL)</sub>	SDA and SCL fall time		300	20+0.1C <sub>b</sub>	300	
t <sub>h(STA)</sub>	START condition hold time	4.0		0.6		
t <sub>su(STA)</sub>	Repeated START condition setup time	4.7		0.6		μS
t <sub>su(STO)</sub>	STOP condition setup time	4.0		0.6		μS
t <sub>w(STO:STA)</sub>	STOP to START condition time (bus free)	4.7		1.3		μS
C <sub>b</sub>	Capacitive load for each bus line		400		400	pF

- 1.  $f_{PCLK}$ , must be at least 8 MHz to achieve max fast  $I^2C$  speed (400 kHz).
- 2. Data based on standard I<sup>2</sup>C protocol requirement, not tested in production.
- 3. The maximum hold time  $t_{h(\mbox{\scriptsize SDA})}$  is not applicable
- 4. The device must internally provide a hold time of at least 300 ns for the SDA signal in order to bridge the undefined region of the falling edge of SCL.

Figure 40. Typical application with I<sup>2</sup>C bus and timing diagram



1. Measurement points are done at CMOS levels:  $0.3xV_{DD}$  and  $0.7xV_{DD}$ .

### 6.3.11 USB characteristics

The USB interface is USB-IF certified (Full Speed).

Table 42. USB startup time

Symbol	Parameter	Conditions	Max	Unit
t <sub>STARTUP</sub>	USB transceiver startup time		1	μs

Table 43. USB characteristics

	USB DC Electrical Characteristics							
Symbol	Parameter	Conditions Mir		Max. <sup>(1)(2)</sup>	Unit			
		Input Levels			•			
V <sub>DI</sub>	Differential Input Sensitivity	I(DP, DM)	0.2					
V <sub>CM</sub>	Differential Common Mode Range	Includes V <sub>DI</sub> range	0.8	2.5	٧			
V <sub>SE</sub>	Single Ended Receiver Threshold		1.3	2.0				
	Output Levels							
V <sub>OL</sub>	Static Output Level Low	$R_L$ of 1.5 k $\Omega$ to 3.6V <sup>(3)</sup>		0.3	V			
V <sub>OH</sub>	Static Output Level High	R <sub>L</sub> of 15 kΩ to $V_{SS}^{(3)}$	2.8	3.6	\ \ \			

<sup>1.</sup> All the voltages are measured from the local ground potential.

3.  $R_L$  is the load connected on the USB drivers

Figure 41. USB: data signal rise and fall time

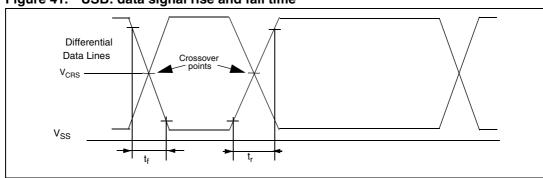


Table 44. USB: Full speed electrical characteristics

Symbol	Parameter	Conditions	Min	Max	Unit		
	Driver characteristics:						
t <sub>r</sub>	Rise time <sup>(1)</sup>	C <sub>L</sub> =50 pF	4	20	ns		
t <sub>f</sub>	Fall Time <sup>1)</sup>	C <sub>L</sub> =50 pF	4	20	ns		

<sup>2.</sup> It is important to be aware that the DP/DM pins are not 5 V tolerant. As a consequence, in case of a a shortcut with Vbus (typ: 5.0V), the protection diodes of the DP/DM pins will be direct biased . This will not damage the device if not more than 50 mA is sunk for longer than 24 hours but the reliability may be affected.

Table 44. USB: Full speed electrical characteristics

Symbol	Parameter	Conditions	Min	Max	Unit
t <sub>rfm</sub>	Rise/ Fall Time matching	t <sub>r</sub> /t <sub>f</sub>	90	110	%
V <sub>CRS</sub>	Output signal Crossover Voltage		1.3	2.0	V

<sup>1.</sup> Measured from 10% to 90% of the data signal. For more detailed informations, please refer to USB Specification - Chapter 7 (version 2.0).

## 6.3.12 10-bit ADC characteristics

Subject to general operating conditions for  $V_{DDA\_ADC}$ ,  $f_{PCLK}$ , and  $T_A$  unless otherwise specified.

Table 45. 10-bit ADC characteristics

Symbol	Parameter	Conditions	Min	Typ <sup>(1)</sup>	Max	Unit
f <sub>ADC</sub>	ADC clock frequency		0.4		8	MHz
V <sub>AIN</sub>	Conversion voltage range <sup>(2)</sup>		V <sub>SSA_ADC</sub>		$V_{DDA\_ADC}$	V
R <sub>AIN</sub>	External input impedance <sup>(3)(4)</sup>				10	kΩ
C <sub>AIN</sub>	External capacitor on analog input <sup>(3)(4)</sup>				6.8	pF
		+400 µA injected on any pin			1	μА
l <sub>lkg</sub>	Induced input leakage current	-400 μA injected on any pin except specific adjacent pins in <i>Table 46</i>			1	μА
		-400μA injected on specific adjacent pins in <i>Table 46</i>		40		μА
C <sub>ADC</sub>	Internal sample and hold capacitor			3.5		pF
+.	Calibration Time	f <sub>CK_ADC</sub> =8 MHz	725.25			μS
t <sub>CAL</sub>	Calibration Time		5802			1/f <sub>ADC</sub>
t <sub>CONV</sub>	Total Conversion time	f <sub>CK_ADC</sub> =8 MHz		3.75		μS
	(including sampling time)		30 (11 for sampling + 19 for Successive Approximation)		1/f <sub>ADC</sub>	
I <sub>ADC</sub>		Sunk on V <sub>DDA_ADC</sub>		3.7		mA

<sup>1.</sup> Unless otherwise specified, typical data are based on  $T_A$ =25°C. They are given only as design guidelines and are not tested.

<sup>2.</sup> Calibration is needed once after each power-up.

C<sub>PARASITIC</sub> represents the capacitance of the PCB (dependent on soldering and PCB layout quality) plus the pad capacitance (3 pF). A high C<sub>PARASITIC</sub> value will downgrade conversion accuracy. To remedy this, f<sub>ADC</sub> should be reduced.

<sup>4.</sup> Depending on the input signal variation ( $f_{AIN}$ ),  $C_{AIN}$  can be increased for stabilization time and reduced to allow the use of a larger serial resistor ( $R_{AIN}$ ). It is valid for all  $f_{ADC}$  frequencies  $\leq 8$  MHz.

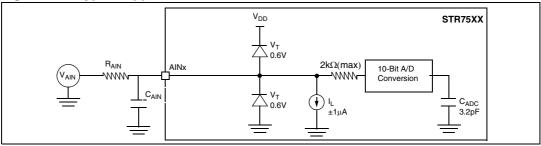
## ADC accuracy vs. negative injection current

Injecting negative current on specific pins listed in *Table 46* (generally adjacent to the analog input pin being converted) should be avoided as this significantly reduces the accuracy of the conversion being performed. It is recommended to add a Schottky diode (pin to ground) to pins which may potentially inject negative current.

Table 46. List of adjacent pins

Analog input	Related adjacent pins
а	None
AIN1/P0.03	None
AIN2/P0.12	P0.11
AIN3/P0.17	P0.18 and P0.16
AIN4/P0.19	P0.24
AIN5/P0.22	None
AIN6/P0.23	P2.04
AIN7/P0.27	P1.11 and P0.26
AIN8/P0.29	P0.30 and P0.28
AIN9/P1.04	None
AIN10/P1.06	P1.05
AIN11/P1.08	P1.04 and P1.13
AIN12/P1.11	P2.17 and P0.27
AIN13/P1.12	None
AIN14/P1.13	P1.14 and P1.01
AIN15/P1.14	None

Figure 42. Typical application with ADC



## Analog power supply and reference pins

The  $V_{DDA\_ADC}$  and  $V_{SSA\_ADC}$  pins are the analog power supply of the A/D converter cell.

Separation of the digital and analog power pins allow board designers to improve A/D performance. Conversion accuracy can be impacted by voltage drops and noise in the event of heavily loaded or badly decoupled power supply lines (see : General PCB design guidelines on page 74).

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## General PCB design guidelines

To obtain best results, some general design and layout rules should be followed when designing the application PCB to shield the noise-sensitive, analog physical interface from noise-generating CMOS logic signals.

- Use separate digital and analog planes. The analog ground plane should be connected to the digital ground plane via a single point on the PCB.
- Filter power to the analog power planes. It is recommended to connect capacitors, with good high frequency characteristics, between the power and ground lines, placing 0.1 μF and optionally, if needed 10 pF capacitors as close as possible to the STR7 power supply pins and a 1 to 10 μF capacitor close to the power source (see Figure 43).
- The analog and digital power supplies should be connected in a star network. Do not use a resistor, as V<sub>DDA\_ADC</sub> is used as a reference voltage by the A/D converter and any resistance would cause a voltage drop and a loss of accuracy.
- Properly place components and route the signal traces on the PCB to shield the analog inputs. Analog signals paths should run over the analog ground plane and be as short as possible. Isolate analog signals from digital signals that may switch while the analog inputs are being sampled by the A/D converter. Do not toggle digital outputs near the A/D input being converted.

### Software filtering of spurious conversion results

For EMC performance reasons, it is recommended to filter A/D conversion outliers using software filtering techniques.

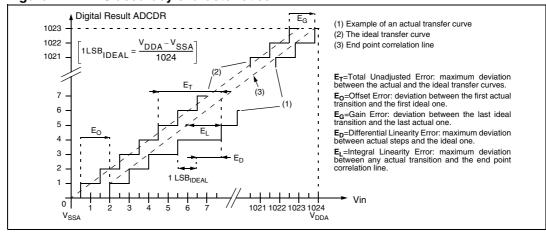
Figure 43. Power supply filtering

Table 47. ADC accuracy

ADC accuracy with $f_{CK\_SYS}$ = 20 MHz, $f_{ADC}$ =8 MHz, $R_{AIN}$ < 10 k $\Omega$ This assumes that the ADC is calibrated <sup>(1)</sup>						
Symbol	Parameter Conditions		Тур	Max	Unit	
IE I	Total unadjusted error (2) (3)	V <sub>DDA_ADC</sub> =3.3 V	1	1.2		
IE <sub>T</sub> I T	Total unadjusted error (700)	V <sub>DDA_ADC</sub> =5.0 V	1	1.2		
IE <sub>O</sub> I Offset	Offset error <sup>(2) (3)</sup>	V <sub>DDA_ADC</sub> =3.3 V	0.15	0.5		
	Oliset ellol ( ) ( )	V <sub>DDA_ADC</sub> =5.0 V	0.15	0.5		
E <sub>G</sub> Ga	Gain Error <sup>(2) (3)</sup>	V <sub>DDA_ADC</sub> =3.3 V	-0.8	-0.2	LSB	
	Gaill Elloi (7)	V <sub>DDA_ADC</sub> =5.0 V	-0.8	-0.2	LOD	
IE I	Differential linearity error <sup>(2) (3)</sup>	V <sub>DDA_ADC</sub> =3.3 V	0.7	0.9		
IE <sub>D</sub> I	Differential linearity error (7)	V <sub>DDA_ADC</sub> =5.0 V	0.7	0.9		
IE <sub>L</sub> I	Integral linearity error (2) (3)	V <sub>DDA_ADC</sub> =3.3 V	0.6	0.8		
	Integral inteatity error (7)	V <sub>DDA_ADC</sub> =5.0 V	0.6	0.8		

- 1. Calibration is needed once after each power-up.
- 2. Refer to ADC accuracy vs. negative injection current on page 73
- ADC Accuracy vs. MCO (Main Clock Output): the ADC accuracy can be significantly degraded when
  activating the MCO on pin P0.01 while converting an analog channel (especially those which are close to
  the MCO pin). To avoid this, when an ADC conversion is launched, it is strongly recommended to disable
  the MCO.

Figure 44. ADC accuracy characteristics

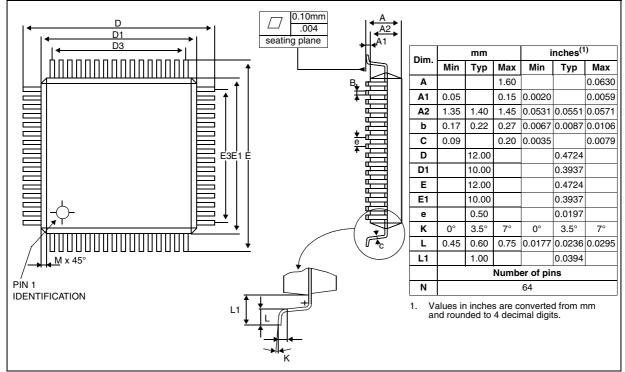


## 7 Package characteristics

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK<sup>®</sup> packages, depending on their level of environmental compliance. ECOPACK<sup>®</sup> specifications, grade definitions and product status are available at: *www.st.com*. ECOPACK<sup>®</sup> is an ST trademark.

## 7.1 Package mechanical data





inches<sup>(1)</sup> mm Dim. Min Max Min Max Typ Typ 0.0630 Α 1.60 0.0059 Α1 0.05 0.15 0.0020 **A2** 1.35 1.40 1.45 0.0531 0.0551 0.0571 0.22 0.27 0.0067 0.0087 0.0106 b 0.17 C 0.09 0.20 0.0035 0.0079 D 16.00 0.6299 D1 14.00 0.5512 Ε 16.00 0.6299 E1 14.00 0.5512 0.50 е 0.0197 7° θ 0° 3.5° 0° 3.5° L 0.45 0.60 0.75 0.0177 0.0236 0.0295 8888888888888888888888888 L1 1.00 0.0394 Number of Pins Ν 100 Values in inches are converted from mm and

rounded to 4 decimal digits.

Figure 46. 100-pin low profile flat package (14x14)

Figure 47. 64-ball low profile fine pitch ball grid array package

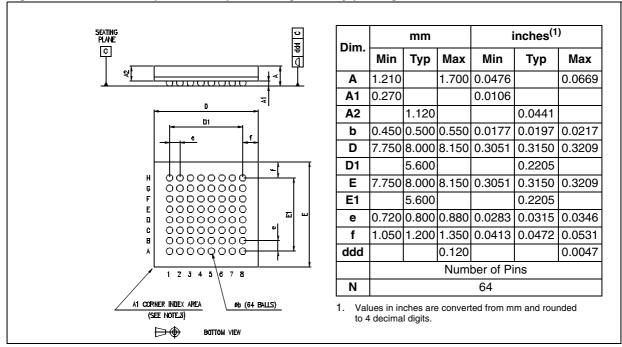
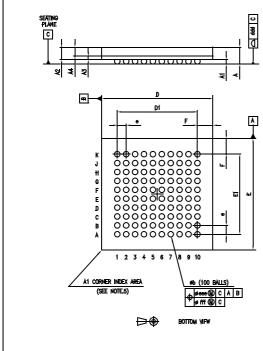


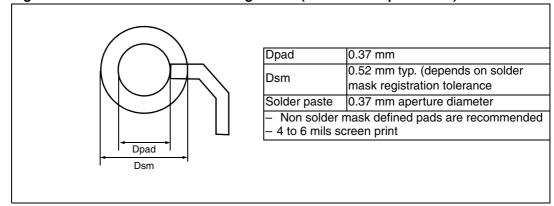
Figure 48. 100-ball low profile fine pitch ball grid array package



Dim.	mm			inches <sup>(1)</sup>			
Dilli.	Min	Тур	Max	Min	Тур	Max	
Α			1.700			0.0669	
A1	0.270			0.0106			
A2		1.085			0.0427		
А3		0.30			0.0118		
<b>A</b> 4			0.80			0.0315	
b	0.45	0.50	0.55	0.0177	0.0197	0.0217	
D	9.85	10.00	10.15	0.3878	0.3937	0.3996	
D1		7.20			0.2835		
E	9.85	10.00	10.15	0.3878	0.3937	0.3996	
E1		7.20			0.2835		
е		0.80			0.0315		
F		1.40			0.055		
ddd			0.12			0.005	
eee			0.15			0.006	
fff			0.08			0.003	
	Number of Balls						
N			10	00			

Values in inches are converted from mm and rounded to 4 decimal digits.

Figure 49. Recommended PCB design rules (0.80/0.75mm pitch BGA)



## 7.2 Thermal characteristics

The maximum chip junction temperature (T<sub>Jmax</sub>) must never exceed the values given in *Table 10: General operating conditions on page 34*.

The maximum chip-junction temperature, T<sub>Jmax</sub>, in degrees Celsius, may be calculated using the following equation:

$$T_{Jmax} = T_{Amax} + (P_{Dmax} \times \Theta_{JA})$$

#### Where:

- T<sub>Amax</sub> is the maximum Ambient Temperature in °C,
- O<sub>,IA</sub> is the Package Junction-to-Ambient Thermal Resistance, in ° C/W,
- $P_{Dmax}$  is the sum of  $P_{INTmax}$  and  $P_{I/Omax}$  ( $P_{Dmax} = P_{INTmax} + P_{I/Omax}$ ),
- P<sub>INTmax</sub> is the product of I<sub>DD</sub> and V<sub>DD</sub>, expressed in Watts. This is the maximum chip internal power.
- P<sub>I/Omax</sub> represents the maximum Power Dissipation on Output Pins. Where:

$$\begin{split} P_{I/Omax} &= \Sigma \left( V_{OL} ^* I_{OL} \right) + \Sigma ((V_{DD} - V_{OH}) ^* I_{OH}), \\ \text{taking into account the actual } V_{OL} \ / \ I_{OL} \ \text{and } V_{OH} \ / \ I_{OH} \ \text{of the I/Os at low and high level in the application.} \end{split}$$

Table 48. Thermal characteristics<sup>(1)</sup>

Symbol	Parameter	Value	Unit
$\Theta_{JA}$	Thermal Resistance Junction-Ambient LQFP 100 - 14 x 14 mm / 0.5 mm pitch	46	°C/W
$\Theta_{JA}$	Thermal Resistance Junction-Ambient LQFP 64 - 10 x 10 mm / 0.5 mm pitch	45	°C/W
$\Theta_{JA}$	Thermal Resistance Junction-Ambient LFBGA 64 - 8 x 8 x 1.7mm	58	°C/W
$\Theta_{JA}$	Thermal Resistance Junction-Ambient LFBGA 100 - 10 x 10 x 1.7mm	41	°C/W

Thermal resistances are based on JEDEC JESD51-2 with 4-layer PCB in a natural convection environment.

### 7.2.1 Reference document

JESD51-2 Integrated Circuits Thermal Test Method Environment Conditions - Natural Convection (Still Air). Available from www.jedec.org

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## 7.2.2 Selecting the product temperature range

When ordering the microcontroller, the temperature range is specified in the order code *Table 49: Order codes on page 81*.

The following example shows how to calculate the temperature range needed for a given application.

Assuming the following application conditions:

Maximum ambient temperature  $T_{Amax}$ = 82 °C (measured according to JESD51-2),  $I_{DDmax}$ =8 mA,  $V_{DD}$  = 5 V, maximum 20 I/Os used at the same time in output at low level with  $I_{OL}$  = 8 mA,  $V_{OL}$ = 0.4 V

$$P_{INTmax} = 8 \text{ mA x 5 V} = 400 \text{ mW}$$
  
 $P_{IOmax} = 20 \text{ x 8 mA x } 0.4 \text{V} = 64 \text{ mW}$ 

This gives: P<sub>INTmax</sub>= 400 mW and P<sub>IOmax</sub> 64 mW:

$$P_{Dmax} = 400 \text{ mW} + 64 \text{ mW}$$

Thus: P<sub>Dmax</sub> = 464 mW

Using the values obtained in Table 48  $T_{Jmax}$  is calculated as follows:

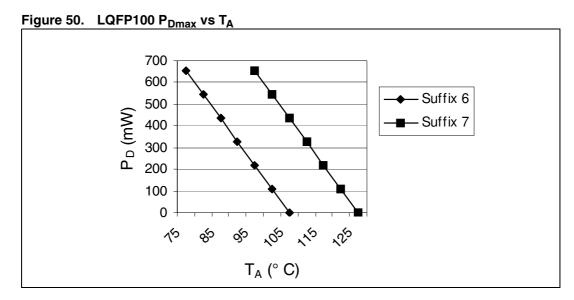
For LQFP100, 46°C/W

$$T_{Jmax} = 82^{\circ} \text{ C} + (46^{\circ} \text{ C/W x } 464 \text{ mW}) = 82^{\circ} \text{C} + 21^{\circ} \text{C} = 103^{\circ} \text{ C}$$
  
This is within the range of the suffix 6 version parts (-40 <  $T_{J}$  < 105° C).  
In this case, parts must be ordered at least with the temperature range suffix 6 (see *Table 49: Order codes on page 81*).

For BGA64, 58°C/W

$$T_{Jmax}=82^{\circ}~C~+~(58^{\circ}~C/W~x~464~mW)=82^{\circ}C~+~27^{\circ}C=109^{\circ}~C$$
 This is within the range of the suffix 7 version parts (-40 < T<sub>J</sub> < 125° C). In this case, parts must be ordered at least with the temperature range suffix 7

(see *Table 49: Order codes on page 81*).



## 8 Order codes

Table 49. Order codes

Order code	Flash Prog. Memory (Bank 0) Kbytes	Package	CAN Periph	USB Periph	Nominal Temp. Range (T <sub>A</sub> )
STR750FV0T6	64				
STR750FV1T6	128	LQFP100 14x14			
STR750FV2T6	256		Yes	Yes	-40 to +85°C
STR750FV0H6	64		162	162	-40 to +65 C
STR750FV1H6	128	LFBGA100 10x10			
STR750FV2H6	256				
STR751FR0T6	64				
STR751FR1T6	128	LQFP64 10x10			-40 to +85°C
STR751FR2T6	256			Yes	
STR751FR0H6	64		_	res	
STR751FR1H6	128	LFBGA64 8x8			
STR751FR2H6	256				
STR752FR0T6	64		Yes	-	-40 to +85°C
STR752FR1T6	128	LQFP64 10x10			
STR752FR2T6	256				
STR752FR0H6	64				
STR752FR1H6	128	LFBGA64 8x8			
STR752FR2H6	256				
STR752FR0T7	64			es -	-40 to +105°C
STR752FR1T7	128	LQFP64 10x10			
STR752FR2T7	256		Voc		
STR752FR0H7	64		Yes		
STR752FR1H7	128	LFBGA64 8x8			
STR752FR2H7	256				
STR755FR0T6	64				
STR755FR1T6	128	LQFP64 10x10			
STR755FR2T6	256				-40 to +85°C
STR755FR0H6	64		] -	-	-40 to +00 C
STR755FR1H6	128	LFBGA64 8x8			
STR755FR2H6	256				

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Table 49. Order codes (continued)

Order code	Flash Prog. Memory (Bank 0) Kbytes	Package	CAN Periph	USB Periph	Nominal Temp. Range (T <sub>A</sub> )
STR755FV0T6	64				
STR755FV1T6	128	LQFP100 14x14			
STR755FV2T6	256		_	_	-40 to +85°C
STR755FV0H6	64		-	-	-40 to +65 C
STR755FV1H6	128	LFBGA100 10x10			
STR755FV2H6	256				

# 9 Revision history

Table 50. Document revision history

Date	Revision	Description of Changes
25-Sep-2006	1	Initial release
30-Oct-2006	2	Added power consumption data for 5V operation in Section 6
04-Jul-2007	3	Changed datasheet title from STR750F to STR750FXX STR751Fxx STR752Fxx STR755xx.  Added Table 1: Device summary on page 1  Added note 1 to Table 6  Added STOP mode IDD max. values in Table 14  Updated XT2 driving current in Table 23.  Updated RPD in Table 32  Updated Table 21: XRTC1 external clock source on page 45  Updated Table 34: Output speed on page 57  Added characteristics for SSP synchronous serial peripheral in master mode (SPI or TI mode) on page 62 and SSP synchronous serial peripheral in slave mode (SPI or TI mode) on page 65  Added characteristics for SMI - serial memory interface on page 68  Added Table 42: USB startup time on page 70
23-Oct-2007	4	Updated Section 6.2.3: Thermal characteristics on page 33 Updated P <sub>D</sub> , T <sub>J</sub> and T <sub>A</sub> in Section 6.3: Operating conditions on page 34 Updated Table 20: XT1 external clock source on page 44 Updated Table 21: XRTC1 external clock source on page 45 Updated Section 7: Package characteristics on page 76 (inches rounded to 4 decimal digits instead of 3) Updated Ordering information Section 8: Order codes on page 81
17-Feb-2009	5	Modified note 3 below <i>Table 8: Current characteristics on page 33</i> Added AHB clock frequency for write access to Flash registers in <i>Table 10: General operating conditions on page 34</i> Modified note 3 below <i>Table 41: SDA and SCL characteristics on page 69</i>

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